

RL78/I1E

RENESAS MCU

R01DS0274EJ0130 Rev. 1.30 Mar 29, 2024

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- VDD= 2.4 to 5.5 V
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.03125 μs: @ 32 MHz operation with high-speed on-chip oscillator or PLL clock)^{Note} to ultra-low speed (1 μs: @ 1 MHz operation with highspeed on-chip oscillator or PLL clock)
- Multiply/divide/multiply & accumulate instructions are supported.
- Address space: 1 MB
- lacktriangle General-purpose registers: (8-bit register imes 8) imes 4 banks
- On-chip RAM: 8 KB

Note

For industrial applications (M; TA = -40 to +125°C): 0.04167 μs @ 24 MHz operation with high-speed on-chip oscillator or PLL clock

Code flash memory

- Code flash memory: 32 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- Self-programming (with boot swap function/flash shield window function)

Data flash memory

- Data flash memory: 4 KB
- Back ground operation (BGO): Instructions can be executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: VDD = 2.4 to 5.5 V

High-speed on-chip oscillator

- Select from 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- ◆ High accuracy:
 ±2.0% (VDD = 2.4 to 5.5 V, TA = -40 to +105°C)
 ±3.0% (VDD = 2.4 to 5.5 V, TA = -40 to +125°C)

Operating ambient temperature

- TA = -40 to +105°C (G: Industrial applications)
- TA = -40 to +125°C (M: Industrial applications)

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 7 levels)

Data transfer controller (DTC)

- Transfer modes: Normal transfer mode, repeat transfer mode, block transfer mode
- Activation sources: Activated by interrupt sources.
- Chain transfer function

Event link controller (ELC)

 Event signals of 16 types can be linked to the specified peripheral function.

Serial interfaces

- Simplified SPI(CSI): 2 channels
- UART: 2 channels (UART with LIN-bus supported: 1 channel)
- I²C/simplified I²C: 2 channels

Timer

- 16-bit timer: 8 channels
 (Timer Array Unit (TAU): 6 channels, timer RJ: 1 channel, timer RG: 1 channel)
- Interval timer: 1 channel
- Real-time clock: 1 channel (calendar for 99 years, alarm function, and clock correction function)
- Watchdog timer: 1 channel (operable with the dedicated low-speed on-chip oscillator)

Analog front-end (AFE) power supply

Sensor power supply (SBIAS) output: 0.5 V to 2.2 V

- 24-bit $\Delta\Sigma$ A/D converter with programmable gain instrumentation amplifier
- 24-bit second-order $\Delta\Sigma$ A/D converter (AVDD = 2.7 to 5.5 V)
- SNDR: 85 dB (TYP.)
- Output data rate:
 488 sps to 15.625 ksps in normal mode
 61 sps to 1.953 ksps in low power mode
- Programmable gain instrumentation amplifier input: 3 or 4 channels (differential input mode or single-ended input mode can be specified for each input channel)
- DAC for offset adjustment
- Variable gain: x1 to x64
- On-chip temperature sensor

10-bit A/D converter

- 8-bit/10-bit successive approximation A/D converter (AVDD = 2.7 to 5.5 V)
- Analog input: 8 or 10 channels, sensor power supply (SBIAS), and internal reference voltage
- Internal reference voltage (1.45 V)

Configurable amplifier

- Matrix configuration that consists of 3 operational amplifier channels and a configurable switch (AVDD = 2.7 to 5.5 V)
- Can be used as a 2- or 3-channel general operational amplifier
- Operational amplifier output: 3 channels
- General-purpose Analog I/O ports: 5 or 6 channels
- Offset voltage calibration

D/A converter

- 12-bit R-2R resistor ladder type D/A converter (AVDD = 2.7 to 5.5 V)
- Analog output: 1 channel (via configurable amplifier)

I/O port

- CMOS I/O: 10 to 14 (N-ch open drain I/O [withstanding voltage of VDD]: 6, CMOS I/O: 7 to 11, CMOS input: 3)
- Can be set to TTL input buffer and on-chip pull-up resistor
- Different potential interface: Can connect to a 2.5/3 V device
- On-chip clock output/buzzer output controller

Others

On-chip BCD (binary-coded decimal) correction circuit

Note Although the CSI function is generally called SPI, it is also called CSI in this product, so it is referred to as such in this manual.

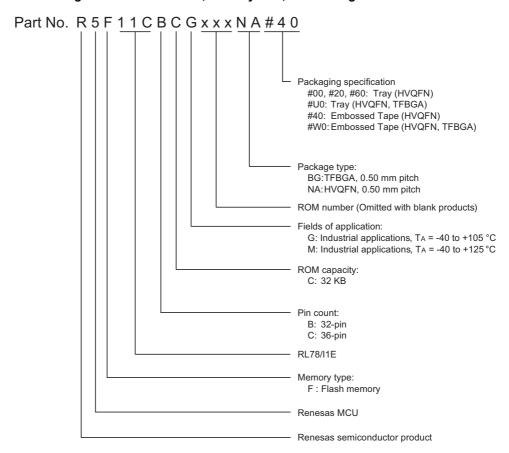
O ROM, RAM capacities

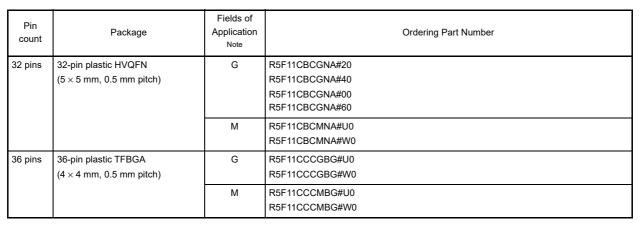
Flash ROM	Data flash	RAM	RL78	3/I1E
Flash ROM Data flash	IVAIVI	32 pins	36 pins	
32 KB	4 KB	8 KB	R5F11CBC	R5F11CCC

1.2 Ordering Information

<R>

Figure 1 - 1 Part Number, Memory Size, and Package of RL78/I1E





Note For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/I1E.

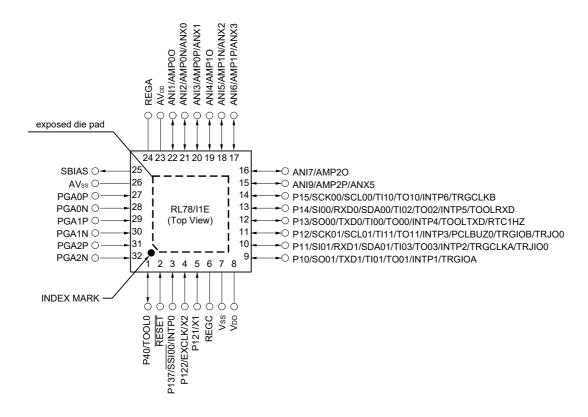
Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3 Pin Configuration (Top View)

1.3.1 32-pin products

• 32-pin plastic HVQFN (5 × 5 mm, 0.5 mm pitch)

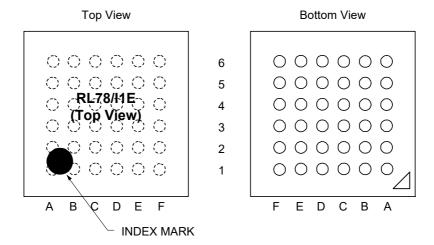


- Caution 1. Connect the REGC pin to the Vss pin via a capacitor (0.47 to 1 $\mu\text{F}).$
- Caution 2. Connect the REGA pin to the AVss pin via a capacitor (0.22 $\mu\text{F}).$
- Caution 3. Make the AVss pin the same potential as the Vss pin.
- Caution 4. Make the AVDD pin the same potential as the VDD pin.
- Caution 5. Connect the SBIAS pin to the AVss pin via a capacitor (0.22 $\mu\text{F}).$

Remark 1. It is recommended to connect an exposed die pad to Vss.

1.3.2 36-pin products

• 36-pin plastic TFBGA (4 × 4 mm, 0.5 mm pitch)



	Α	В	С	D	E	F	
6	PGA2P	PGA1N	PGA1P	PGA0P	PGA3P	AVss	6
5	PGA2N	P40/TOOL0	PGA0N	PGA3N	REGA	SBIAS	5
4	RESET	P137/SSI00/ INTP0	P11/SI01/RXD1/ SDA01/TI03/ TO03/INTP2/ TRGCLKA/	P12/SCK01/ SCL01/TI11/ TO11/INTP3/ PCLBUZ0/	ANIO	AVDD	4
3	P122/EXCLK/X2	P15/SCK00/ SCL00/T110/ TO10/INTP6/ TRGCLKB	TRJIO0 P10/SO01/TXD1/ TI01/TO01/ INTP1/TRGIOA	TRGIOB/TRJO0 ANI3/AMP0P/ ANX1	ANI2/AMPON/ ANX0	ANI1/AMP0O	3
2	P121/X1	REGC	P14/SI00/RXD0/ SDA00/TI02/ TO02/INTP5/ TOOLRXD	P41/ANI6/ AMP1P/ANX3	P42/ANI5/ AMP1N/ANX2	ANI4/AMP1O	2
1	VDD	Vss	P13/SO00/TXD0/ TI00/TO00/INTP4/ TOOLTXD/ RTC1HZ	P16/INTP7/ANI9/ AMP2P/ANX5	P17/ANI8/ AMP2N/ANX4	ANI7/AMP2O	1
	Α	В	С	D	E	F	

Caution 1. Connect the REGC pin to the Vss pin via a capacitor (0.47 to 1 μ F).

Caution 2. Connect the REGA pin to the AVss pin via a capacitor (0.22 μF).

Caution 3. Make the AVss pin the same potential as the Vss pin.

Caution 4. Make the AVDD pin the same potential as the VDD pin.

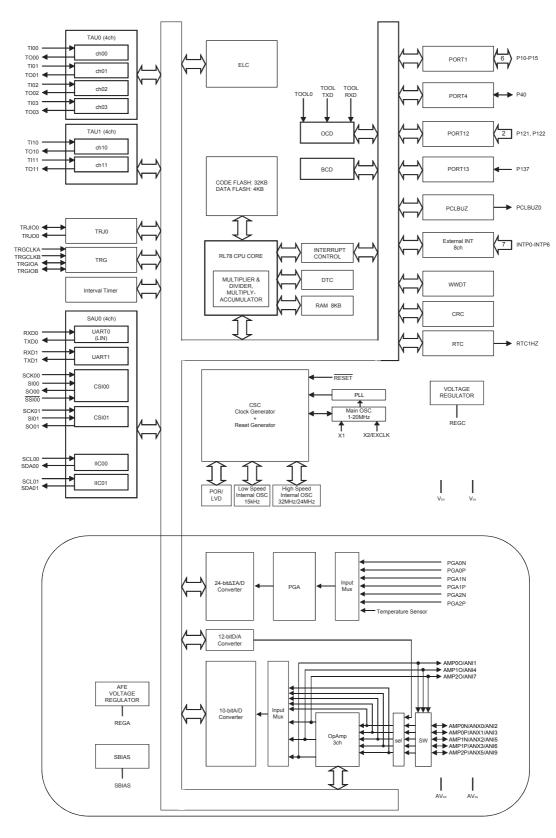
Caution 5. Connect the SBIAS pin to the AVss pin via a capacitor (0.22 $\mu\text{F}).$

1.4 Pin Identification

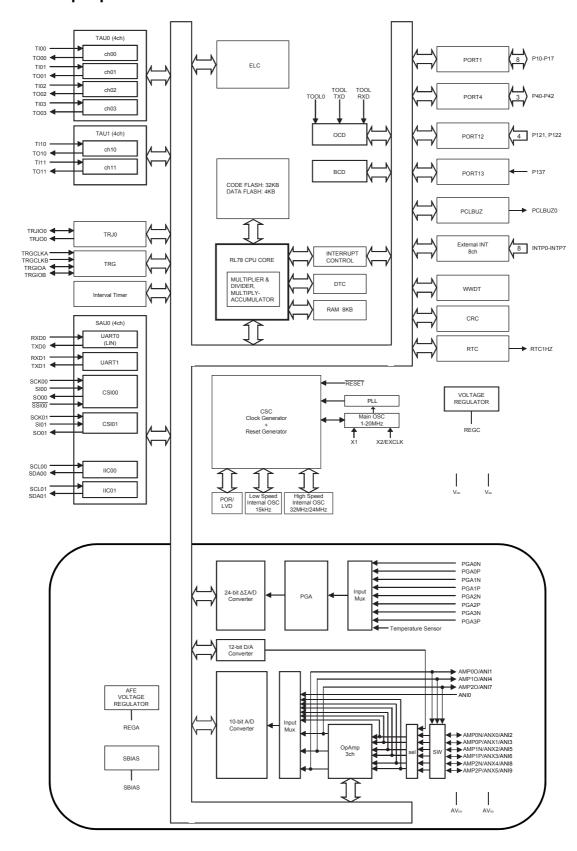
ANI0 to ANI9: RESET: Analog input Reset AMP0P to AMP2P: Operational amplifier REGA: Regulator capacitance for analog positive input REGC: Regulator capacitance AMP0N to AMP2N: Operational amplifier RTC1HZ: Real-time clock correction negative input RxD0, RxD1: Receive data AMP0O to AMP2O: Operational amplifier output Bias output for MEMS sensor SBIAS: ANX0 to ANX5: General-purpose analog SCK00, SCK01: Serial clock input/output ports for operational amplifier SCL00, SCL01: Serial clock output AVDD: Power supply for analog SI00, SI01: Serial data input AVss: Ground for analog SO00, SO01: Serial data output EXCLK: TI00 to TI03, TI10, TI11: External clock input Timer input (main system clock) TO00 to TO03, TO10, TO11, Timer output INTP0 to INTP7: TRJO0: External interrupt input P10 to P17: TOOL0: Port 1 Data input/output for tools P40 to P42: TOOLRxD, TOOLTxD: Port 4 Data input/output for external devices P121, P122: TRGCLKA, TRGCLKB: Port 12 Timer external clock input P137: TRGIOA, TRGIOB, TRJIO0: Port 13 Timer input/output PCLBUZ0: TxD0, TxD1: Programmable clock output/ Transmit data buzzer output VDD: Power supply PGA0N to PGA3N: PGA negative analog input Vss: Ground PGA0P to PGA3P: PGA positive analog input X1, X2: Crystal oscillator (main system clock)

1.5 Block Diagram

1.5.1 32-pin products



1.5.2 36-pin products



1.6 Outline of Functions

[32-pin, 36-pin products]

(1/2)

			(1/2)			
	Item	32-pin	36-pin			
		R5F11CBC	R5F11CCC			
Code flash men	mory	32 KB				
Data flash mem	nory	4 KB				
RAM		8 KB				
Address space		1 MB				
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system 1 to 20 MHz: VDD = 2.7 to 5.5 V, 1 to 16 MHz: VDD				
	High-speed on-chip oscillator clock (fін)	1 to 32 MHz (V _{DD} = 2.7 to 5.5 V) ^{Note 1} 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V)				
	PLL clock (fPLL divided by 2, 4, or 8)	3 to 32 MHz (V _{DD} = 2.7 to 5.5 V) ^{Note 2} 3 to 16 MHz (V _{DD} = 2.4 to 5.5 V)				
General-purpos	se register	8 bits × 32 registers (8 bits × 8 registers × 4 banks)				
Minimum instru	ction execution time	0.03125 μs (high-speed on-chip oscillator clock: fiн =	: 32 MHz operation) ^{Note 3}			
		0.03125 μs (PLL clock: fPLL = 64 MHz, fiн = 32 MHz operation)Note 4				
		0.05 μs (high-speed system clock: fмx = 20 MHz operation)				
Instruction set		 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits, 16 bits × 16 bits), division (16 bits + 16 bits, 32 bits + 32 bits) Multiplication and Accumulation (16 bits × 16 bits + 32 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 				
I/O port	Total	10	14			
	CMOS I/O	7	11			
	CMOS input	3	3			
Timer	16-bit timer	8 channels (TAU: 6 channels, Timer RJ: 1 channel,	limer RG: 1 channel)			
	Watchdog timer	1 channel				
	Real-time clock (RTC)	1 channel				
	Interval timer	1 channel				
	Timer output	Timer outputs: 10 channels PWM outputs: 9 channels				
	RTC output	1				
Clock output/bu	ızzer output	1				
		2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 (Main system clock: fmain = 20 MHz operation)	MHz, 10 MHz			
8/10-bit A/D cor	nverter	8 channels	10 channels			
Serial interface		Simplified SPI(CSI): 2 channels/UART: 2 channels (UART supporting LIN-bus: 1 channel)/simplified I ² C: 2 channels				

- Note 1. 1 to 24 MHz (VDD = 2.7 to 5.5 V) for M products (industrial applications, $T_A = -40$ to $+125^{\circ}C$)
- **Note 2.** 3 to 24 MHz (VDD = 2.7 to 5.5 V) for M products (industrial applications, $T_A = -40$ to $+125^{\circ}$ C)
- Note 3. 0.04167 μ s (high-speed on-chip oscillator clock: fiH = 24 MHz operation) for M products (industrial applications, TA = -40 to +125°C)
- Note 4. 0.04167 µs (PLL clock: fPLL = 64 MHz, fill = 24 MHz operation) for M products (industrial applications, Ta = -40 to +125°C

(2/2)

			. ,			
	tom	32-pin	36-pin			
'	tem	R5F11CBC	R5F11CCC			
Data transfer contro	ller (DTC)	22 sources				
Event link controller	(ELC)	Event input: 16 Event trigger output: 7				
Vectored interrupt	Internal	23	23			
sources	External	7	8			
ΔΣ A/D converter	24-bit	3 channels	4 channels			
	AFE temperature sensor	1 channel				
Operational 3-pin		3 channels Note 1	3 channels			
port general-purpose	5 channels	6 channels				
D/A converter	12-bit	1 channel				
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note 2 Internal reset by RAM parity error Internal reset by illegal-memory access				
Power-on-reset circ	uit	Power-on-reset: 1.56 ±0.03 V Power-down-reset: 1.55 ±0.03 V				
Voltage detector		At rise: 2.55 V to 4.64 V (7 steps) At fall: 2.61 V to 4.74 V (7 steps)				
On-chip debug func	tion	Provided				
Power supply voltage	je	V _{DD} = 2.4 to 5.5 V				
Operating ambient t	emperature	$T_A = -40 \text{ to } +105^{\circ}\text{C}$ (G: Industrial applications), $T_A = -40 \text{ to } +105^{\circ}\text{C}$:-40 to +125°C (M: Industrial applications)			
D/A converter Reset Power-on-reset circular Voltage detector On-chip debug function Power supply voltage	General-purpose port 12-bit uit tion	5 channels 1 channel Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note 2 Internal reset by RAM parity error Internal reset by illegal-memory access Power-on-reset: 1.56 ±0.03 V Power-down-reset: 1.55 ±0.03 V At rise: 2.55 V to 4.64 V (7 steps) At fall: 2.61 V to 4.74 V (7 steps) Provided VDD = 2.4 to 5.5 V	6 channels			

- **Note 1.** When each of the 3 channels is in use as an independent amplifier, at least one channel must be in a voltage follower configuration.
- Note 2. The illegal instruction is generated when instruction code FFH is executed.

 Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS (G: TA = -40 to +105°C)

This chapter describes the electrical specifications for the products "G: Industrial applications (TA = -40 to +105°C)".

- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. The pins mounted depend on the product.
- Caution 3. Please contact Renesas Electronics sales office for derating of operation under TA = +85 to +105°C.

 Derating is the systematic reduction of load for the sake of improved reliability.
- **Remark** The electrical characteristics of the products G: Industrial applications (TA = -40 to +105°C) are different from those of the products "M: Industrial applications". For details, refer to **2.1** to **2.10**.

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings

(1/2)

Parameter	Symbol	Cond	litions	Ratings	Unit
Supply voltage	VDD			-0.5 to +6.5	V
	AVDD	AVDD = VDD		-0.5 to +6.5	V
	AVss	AVss = Vss		-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC		-0.3 to +2.8 and -0.3 to V _{DD} + 0.3 ^{Note 1}	V
REGA pin input voltage	VIREGA	REGA		-0.3 to +2.8 and -0.3 to AV _{DD} + 0.3 ^{Note 2}	V
Input voltage	VI1	P10 to P15, P40, P121 RESET	, P122, P137, EXCLK,	-0.3 to V _{DD} +0.3 Note 3	V
Alternate-function pin	VI2	P16, P17, P41, P42	Digital input voltage	-0.3 to V _{DD} + 0.3 Note 3	V
input voltage		(36-pin products only)	Analog input voltage	-0.3 to AV _{DD} + 0.3 Note 3	V
Analog input voltage	VIA	PGA0P to PGA3P, PGANIO to ANIO to ANIO, ANXO to	,	-0.3 to AV _{DD} + 0.3 Note 3	V
Output voltage	Vo1	P10 to P15, P40		-0.3 to V _{DD} + 0.3 Note 3	V
Alternate-function pin	VO2	P16, P17, P41, P42	Digital output voltage	-0.3 to V _{DD} + 0.3 Note 3	V
output voltage		(36-pin products only)	Analog output voltage	-0.3 to AV _{DD} + 0.3 Note 3	V
Analog output voltage	Voa	SBIAS, AMP0O to AMF	P2O, ANX0 to ANX5	-0.3 to AV _{DD} + 0.3 Note 3	V

- Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
- **Note 2.** Connect the REGA pin to AVss via a capacitor (0.22 μ F). This value regulates the absolute maximum rating of the REGA pin. Do not use this pin with voltage applied to it.
- Note 3. Must be 6.5 V or lower.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

 That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. Vss is used as the reference voltage.

Absolute Maximum Ratings

(2/2)

Parameter	Symbol		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P10 to P17, P40 to P42	-40	mA
		Total of all pins	P10 to P17, P41, P42 Note	-100	mA
Analog output current,	Іона	Per pin	AMP0O to AMP2O	-12	mA
high			ANX0 to ANX5	-0.12	mA
		Total of all pins	AMP0O to AMP2O, ANX0 to ANX5	-18	mA
Output current, low	IOL1	Per pin	P10 to P17, P40 to P42	40	mA
		Total of all pins	P10 to P17, P41, P42 Note	100	mA
Analog output current, low	IOLA	Per pin	AMP0O to AMP2O	12	mA
			ANX0 to ANX5	0.12	mA
		Total of all pins	AMP0O to AMP2O, ANX0 to ANX5	18	mA
Operating ambient	TA	In normal operation	on mode	-40 to +105	°C
temperature		In flash memory programming mode			
Storage temperature	Tstg			-65 to +150	°C

Note This indicates the total current value when P16, P17, P41, and P42 are used as digital input pins.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Remark 2. Vss is used as the reference voltage.

2.2 Oscillator Characteristics

2.2.1 X1 characteristics

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{AVDD} = \text{VDD} \le 5.5 \text{ V}, \text{AVss} = \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	1.0		20.0	MHz
	crystal resonator	$2.4 \text{ V} \leq \text{Vdd} \leq 2.7 \text{ V}$	1.0		16.0	

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time.

Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

2.2.2 On-chip oscillator characteristics

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency	fıн	2.7 V ≤ VDD ≤ 5.5 V		1		32	MHz
Notes 1, 2		2.4 V ≤ V _{DD} < 2.	7 V	1		16	MHz
High-speed on-chip oscillator clock frequency accuracy		-40 to +105°C	2.4 V ≤ VDD ≤ 5.5 V	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 3 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

2.2.3 PLL characteristics

(Ta = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol		Conditions			TYP.	MAX.	Unit
PLL output frequencyNotes 1, 2,	fPLL	fmx = 8 MHz	DSFRDIV = 0	DSCM = 0		48		MHz
3				DSCM = 1		64		MHz
			DSFRDIV = 1	DSCM = 0		24		MHz
				DSCM = 1		32		MHz
		fmx = 4 MHz	DSFRDIV = 0	DSCM = 0		24		MHz
				DSCM = 1		32		MHz
Lockup wait time		Time from who	en PLL output is en d	abled to when the	40			μs
Interval wait time			en the PLL stops op PLL operation is s	perating to when the	4			μs
Setup wait time				input clock stabilizes to when the PLL is	1			μs

- Note 1. When using a PLL, input a clock of 4 MHz or 8 MHz to the PLL.
- **Note 2.** Be sure to specify one of these settings when using a PLL.
- Note 3. When using the PLL output as the CPU clock, f_{iH} is divided by 2, 4, or 8 according to the setting of the RDIV1 and RDIV0 hits

2.3 DC Characteristics

2.3.1 Pin characteristics

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le AVDD = VDD \le 5.5 \text{ V}, AVSS = VSS = 0 \text{ V})$

(1/3)

Item	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P10 to P17 and P40 to P42 Note 2	-40°C < Ta ≤ +85°C			-10.0 Note 3	mA
			85°C < Ta ≤ 105°C			-3.0 Note 3	mA
		Total of P10 to P17, P41, and P42 Note 2	4.0 V ≤ VDD ≤ 5.5 V -40°C < TA ≤ +85°C			-80.0	mA
		8	4.0 V ≤ VDD ≤ 5.5 V 85°C < TA ≤ 105°C			-30.0	mA
			2.7 V ≤ V _{DD} < 4.0 V			-19.0	mA
			2.4 V ≤ VDD < 2.7 V			-10.0	mA
Output current, low Note 1	IOL1	Per pin for P10 to P17 and P40 to P42 Note 2	-40°C < TA ≤ +85°C		20.0 Note 3	mA	
			85°C < Ta ≤ 105°C			8.5 Note 3	mA
		Total of P10 to P17, P41, and P42 Note 2	4.0 V ≤ VDD ≤ 5.5 V -40°C < TA ≤ +85°C			80.0	mA
		(When duty ≤ 70% ^{Note 4})	4.0 V ≤ VDD ≤ 5.5 V 85°C < TA ≤ 105°C			40.0	mA
			2.7 V ≤ V _{DD} < 4.0 V			35.0	mA
			2.4 V ≤ V _{DD} < 2.7 V			20.0	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin.
- **Note 2.** This indicates the total current value when P16, P17, P41, and P42 are used as digital I/O ports. When using these pins as analog function (AFE) pins, refer to **2.1 Absolute Maximum Ratings**.
- Note 3. Do not exceed the total current value.
- **Note 4.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$

Example: n = 80% when IOH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Caution P10 to P15 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(Ta = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

(2/3)

Item	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P10 to P17 and P40 to P42	Normal input buffer	0.8 VDD		VDD	٧
	VIH2	P11, P12, P14,	TTL input buffer, 4.0 V ≤ V _{DD} ≤ 5.5 V	2.2		VDD	V
		P15	TTL input buffer, 3.3 V ≤ V _{DD} < 4.0 V	2.0		VDD	V
			TTL input buffer, 2.4 V ≤ V _{DD} < 3.3 V	1.5		VDD	V
	VIH3	P121, P122, P13	7, EXCLK, RESET	0.8 Vdd		VDD	V
Input voltage, low	VIL1	P10 to P17 and P40 to P42	Normal input buffer	0		0.2 VDD	V
	VIL2	P11, P12, P14,	TTL input buffer, 4.0 V ≤ V _{DD} ≤ 5.5 V	0		0.8	V
		P15	TTL input buffer, 3.3 V ≤ V _{DD} < 4.0 V	0		0.5	V
			TTL input buffer, 2.4 V ≤ V _{DD} < 3.3 V	0		0.32	V
	VIL3	P121, P122, P13	7, EXCLK, RESET	0		0.2 VDD	V
Output voltage, high	Vон1	P10 to P17 and P40 to P42	4.0 V ≤ V _{DD} ≤ 5.5 V, T _A = -40 to +85°C, l _{OH1} = -10.0 mA	VDD - 1.5			V
			4.0 V ≤ V _{DD} ≤ 5.5 V, 85°C < T _A ≤ 105°C, I _{OH1} = -3.0 mA	VDD - 0.7			٧
			2.7 V ≤ V _{DD} ≤ 5.5 V, I _{OH1} = -2.0 mA	VDD - 0.6			V
			2.4 V ≤ V _{DD} ≤ 5.5 V, I _{OH1} = -1.5 mA	VDD - 0.5			V
Output voltage, low	VOL1	P10 to P17 and P40 to P42	4.0 V ≤ V _{DD} ≤ 5.5 V, T _A = -40 to +85°C, lo _{L1} = 20.0 mA			1.3	V
			4.0 V ≤ V _{DD} ≤ 5.5 V, 85°C < T _A ≤ 105°C, lo _{L1} = 8.5 mA			0.7	V
			$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}, \text{ lol1} = 3.0 \text{ mA}$			0.6	V
			$2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{ IOL1} = 1.5 \text{ mA}$			0.4	V
			$2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{ IOL1} = 0.6 \text{ mA}$			0.4	V

Caution The maximum V_{IH} value on P10 to P15 is V_{DD} , even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(Ta = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

(3/3)

Item	Symbol	Cond	litions		MIN.	TYP.	MAX.	Unit
Input leakage	ILIH1	P10 to P17, and P40 to P42	VI = VDD				1	μΑ
current, high	ILIH2	P137, RESET	VI = VDD				1	μΑ
	Ішнз	P121, P122 (X1, X2, EXCLK)	VI = VDD	In input port mode or when using external clock input			1	μА
				When a resonator is connected			10	μΑ
Input leakage	ILIL1	P10 to P17, and P40 to P42	Vı = Vss	VI = VSS			-1	μΑ
current, low	ILIL2	P137, RESET	Vı = Vss				-1	μΑ
	ILIL3	P121, P122 (X1, X2, EXCLK)	VI = Vss	In input port mode or when using external clock input			-1	μА
				When a resonator is connected			-10	μА
On-chip pull-up resistance	Ru	P10 to P15, P40	Vı = Vss, in input port mode		10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(1/2)

Parameter	Symbol		Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	fHOCO = 32 MHz, fMAIN = 32 MHz Note 3	Basic	V _{DD} = 5.0 V		2.1		mA
current Note 1		mode ^{Note 2}		operation	V _{DD} = 3.0 V		2.1		
Note 1			fhoco = 32 MHz, fmain = 32 MHz Note 3	Normal	V _{DD} = 5.0 V		4.8	8.7	mA
				operation	V _{DD} = 3.0 V		4.8	8.7	
			fHOCO = 24 MHz, fMAIN = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		3.8	6.7	
				operation	V _{DD} = 3.0 V		3.8	6.7	
			fhoco = 16 MHz, fmain = 16 MHz Note 3	Normal	V _{DD} = 5.0 V		2.8	4.9	
				operation	V _{DD} = 3.0 V	3.3 5.7 3.5 5.8 3.3 5.7 3.5 5.8	4.9		
			fmx = 20 MHz, fmain = 20 MHz Note 4,	Normal	Square wave input		3.3	5.7	mA
	f _{MX} = 20 MHz, f _{MAIN} = 20 MHz ^{Note 4} , Normal Square wave input		V _{DD} = 5.0 V	operation	Resonator connection		3.8 6.7 3.8 6.7 2.8 4.9 2.8 4.9 3.3 5.7 3.5 5.8 3.3 5.7 3.5 5.8	5.8	
		Square wave input		3.3	5.7				
		V _{DD} = 3.0 V operation Resonator connection	Resonator connection		3.5	5.8			
			fmx = 10 MHz, fmain = 10 MHz Note 4,	Normal	Square wave input		2.0	3.4	
			V _{DD} = 5.0 V	operation	Resonator connection		2.1	3.5	
			fmx = 10 MHz, fmain = 10 MHz Note 4,	Normal	Square wave input		2.0	3.4	
			V _{DD} = 3.0 V	operation	Resonator connection		2.1	3.5	
			fmx = 8 MHz, fmain = 32 MHz Note 5,	Normal	Square wave input		5.2	9.2	mA
			V _{DD} = 5.0 V	operation	Resonator connection		5.3	9.3	
			fmx = 8 MHz, fmain = 32 MHz Note 5,	Normal	Square wave input		5.2	9.2	
			V _{DD} = 3.0 V	operation	Resonator connection		5.3	9.3	
			fmx = 8 MHz, fmain = 24 MHz Note 5,	Normal	Square wave input		5.1	9.1	
		V _{DD} = 5.0 V	VDD = 5.0 V	operation	Resonator connection		5.2	9.2	
			fmx = 8 MHz, fmain = 24 MHz Note 5,	Normal	Square wave input		5.1	9.1	
			V _{DD} = 3.0 V	operation	Resonator connection		5.2	9.2	

- Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the RTC, interval timer, watchdog timer, LVD circuit, AFE, I/O ports, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- **Note 2.** The relationship between the operation voltage range and the CPU operating frequency is as below. $2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V} \textcircled{2} 1 \text{ MHz}$ to 32 MHz
- $2.4~V \le V \text{DD} \le 5.5~V~\textcircled{0}~1~\text{MHz}~to~16~\text{MHz}$ Note 3. When the high-speed system clock is stopped
- Note 4. When the high-speed on-chip oscillator and the PLL are stopped
- Note 5. When the high-speed on-chip oscillator is stopped and the PLL is operating
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency
- Remark 3. fmain: Main system clock frequency
- Remark 4. The temperature condition for the TYP. value is TA = 25°C

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

(2/2)

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Supply current	IDD2	HALT mode	fhoco = 32 MHz, fmain = 32 MHz Note 4	V _{DD} = 5.0 V		0.54	3.67	mA
Note 1	Note 2	Note 3		V _{DD} = 3.0 V		0.54	3.67	
			fhoco = 24 MHz, fmain = 24 MHz Note 4	V _{DD} = 5.0 V		0.44	2.85	
			V _{DD} = 3.0 V 0.44 2	2.85				
			fhoco = 16 MHz, fmain = 16 MHz Note 4	V _{DD} = 5.0 V		0.40	2.08	
				V _{DD} = 3.0 V		0.40	2.08	
			fmx = 20 MHz, fmain = 20 MHz Note 5, VDD = 5.0 V	Square wave input		0.28	2.45	mA
				Resonator connection		0.49	2.57	
			f_{MX} = 20 MHz, f_{MAIN} = 20 MHz $^{Note 5}$, V_{DD} = 3.0 V	Square wave input		0.28	2.45	
				Resonator connection		0.49	2.57	
			fmx = 10 MHz, fmain = 10 MHz Note 5, VDD = 5.0 V	Square wave input		0.19	1.28	
				Resonator connection		0.30	1.36	
			fmx = 10 MHz, fmain = 10 MHz Note 5, VDD = 3.0 V	Square wave input		0.19	1.28	
				Resonator connection		0.30	1.36	
			fmx = 8 MHz, fmain = 32 MHz Note 6, VDD = 5.0 V	Square wave input		0.91	4.17	mA
				Resonator connection		1.01	4.27	
			f_{MX} = 8 MHz, f_{MAIN} = 32 MHz Note 6, V_{DD} = 3.0 V	Square wave input		0.91	4.17	
				Resonator connection		1.01	4.27	
			fmx = 8 MHz, fmain = 24 MHz Note 6, VDD = 5.0 V	Square wave input		0.76	3.27	
				Resonator connection		0.86	3.37	
			f_{MX} = 8 MHz, f_{MAIN} = 24 MHz Note 6, V_{DD} = 3.0 V	Square wave input		0.76	3.27	
				Resonator connection		0.86	3.37	
	IDD3	STOP mode	T _A = -40°C	•		0.38	1.14	μΑ
	Note 7		T _A = +25°C			0.50	1.14	
			T _A = +50°C			0.66	4.52	
			T _A = +70°C			1.04	7.98	
			T _A = +85°C			2.92	16.0	
			T _A = +105°C			11.0	100.0	

- Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the RTC, interval timer, watchdog timer, LVD circuit, AFE, I/O ports, and on-chip pull-up/pull-down resistors and the current flowing during writing to the data flash.
- Note 2. During HALT instruction execution from flash memory
- **Note 3.** The relationship between the operation voltage range and the CPU operating frequency is as below. $2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V} \textcircled{2} 1 \text{ MHz}$ to 32 MHz
 - $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ @ 1 MHz to 16 MHz
- Note 4. When the high-speed system clock is stopped
- Note 5. When the high-speed on-chip oscillator and the PLL are stopped
- Note 6. When high-speed on-chip oscillator is stopped and the PLL is operating
- **Note 7.** The MAX. value includes the leakage current in STOP mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency
- Remark 3. fMAIN: Main system clock frequency
- Remark 4. The temperature condition for the TYP. value is TA = 25°C, except the operation in STOP mode.

· Peripheral functions

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol	Conditi	ions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I _{FIL} Note 1				0.20		μА
RTC operating current	I _{RTC} Notes 1, 2, 3	fmx = 4 MHz, RTCCL = 00H (fm)	x = 4 MHz, RTCCL = 00H (fmx/122)				μΑ
Interval timer operating current	_{IT} Notes 1, 2, 4	mx = 4 MHz, RTCCL = 00H (fmx/122)			22		μΑ
Watchdog timer operating current	I _{WDT} Notes 1, 5, 6	fi∟ = 15 kHz			0.22		μΑ
LVD operating current	I _{LVD} Notes 1, 7				0.08		μΑ
Self-programming operating current	I _{FSP} Notes 1, 8				2.50	12.20	mA
BGO operating current	I _{BGO} Notes 1, 9				2.50	12.20	mA
SNOOZE operating	I _{SNOZ} Note 1	A/D converter operation ^{Notes}	The mode is performed		0.50	1.10	mA
current		10,	During A/D conversion, AV _{DD} = V _{DD} = 3.0 V		1.20	2.04	
		Simplified SPI(CSI)/UART oper	ration		0.70	1.54	
		DTC operation			3.10		

- Note 1. Current flowing to VDD
- Note 2. When the high-speed on-chip oscillator is stopped
- Note 3. Current flowing only to the real-time clock (RTC). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock is operating in operation mode or HALT mode.
- Note 4. Current flowing only to the interval timer. The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the interval timer is operating in operation mode or HALT mode. When the low-speed onchip oscillator is selected, also add IFIL.
- Note 5. When the high-speed on-chip oscillator and high-speed system clock are stopped.
- Note 6. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).

 The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is operating.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is operating.
- Note 8. Current flowing during self-programming
- Note 9. Current flowing during writing to the data flash
- Note 10. The current flowing into the AV_{DD} is included.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fil: Low-speed on-chip oscillator clock frequency
- **Remark 3.** The temperature condition for the TYP. value is TA = 25° C

AFE functions

(Ta = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
24-bit $\Delta\Sigma$ A/D converter operating current	IDSAD	Normal mode Notes 1, 2 Circuits that operate: ABGR, REGA, SBIAS, VREFAMP, PGA, 24-bit $\Delta\Sigma$ A/D converter, and digital filter Differential input mode OSR = 256 SBIAS lout = 0 mA		0.94	1.46	mA
		Low power mode Notes 1, 2 Circuits that operate: ABGR, REGA, SBIAS, VREFAMP, PGA, 24-bit $\Delta\Sigma$ A/D converter, and digital filter Differential input mode OSR = 256 SBIAS lout = 0 mA		0.60	0.91	mA
10-bit A/D converter operating current	IADC	During conversion at the highest speed Notes 1, 2 AV _{DD} = 5.0 V		1.30	1.70	mA
Configurable amplifier operating current	Іамр	Normal mode Notes 1, 2 Circuits that operate: ABGR and configurable amplifier IL = 0 mA Per channel		0.13	0.24	mA
		High-speed mode Notes 1, 2 Circuits that operate: ABGR and configurable amplifier IL = 0 mA Per channel		0.30	0.45	mA
12-bit D/A converter operating current	Idac	When AV _{DD} is selected as the reference voltage ^{Notes 1, 2} Circuits that operate: ABGR and internal reference voltage (VREFDA)		0.61	0.97	mA

Note 1. Current flowing to AVDD

Note 2. Current flowing only to the circuits that operate shown in the Conditions column.

2.4 AC Characteristics

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

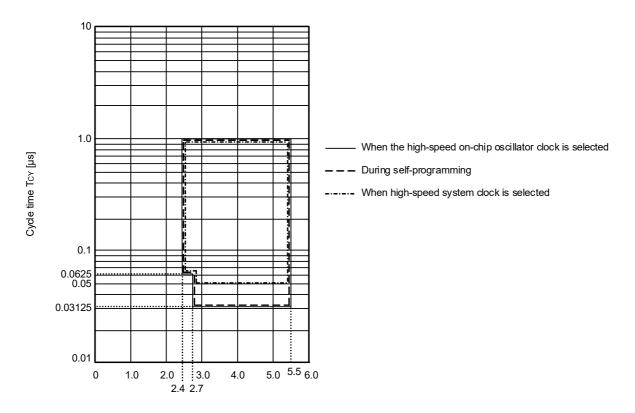
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle	Tcy	Main system clock (fMAIN) operation	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	0.03125		1	μs
(minimum instruction			2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
execution time)		In the self-programming mode	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	0.03125		1	μs
			2.4 V ≤ VDD < 2.7 V	0.0625		1	μs
External system clock	fex	2.7 V ≤ VDD ≤ 5.5 V		1.0		20.0	MHz
frequency		2.4 V ≤ VDD < 2.7 V		1.0		16.0	MHz
External system clock	texH,	2.7 V ≤ VDD ≤ 5.5 V		24			ns
input high-level width, low-level width	texL	2.4 V ≤ V _{DD} < 2.7 V		30			ns
TI00 to TI03, TI10, TI11 input high-level width, low-level width	ttih, ttil			1/fмск + 10			ns
Timer RJ input cycle	fc	TRJI00	2.7 V ≤ VDD ≤ 5.5 V	100			ns
			2.4 V ≤ V _{DD} < 2.7 V	300			ns
Timer RJ input high-	tтлн,	TRJI00	2.7 V ≤ VDD ≤ 5.5 V	40			ns
level width, low-level width	t⊤JIL		2.4 V ≤ V _{DD} < 2.7 V	120			ns
Timer RG input high- level width, low-level width	tтgін, tтgіl	TRGIOA, TRGIOB	•	2.5/fclk			ns
TO00 to TO03,	fто		4.0 V ≤ VDD ≤ 5.5 V			16	MHz
TO10, TO11,			$2.7 \text{ V} \leq \text{VDD} \leq 4.0 \text{ V}$			8	MHz
TRJIO0, TRJO0, TRGIOA, TRGIOB output frequency			2.4 V ≤ V _{DD} < 2.7 V			4	MHz
PCLBUZ0 output	fPCL		4.0 V ≤ V _{DD} ≤ 5.5 V			16	MHz
frequency			2.7 V ≤ V _{DD} ≤ 4.0 V			8	MHz
			2.4 V ≤ V _{DD} < 2.7 V			4	MHz
Interrupt input high- level width, low-level width	tinth, tintl	INTP1 to INTP7	I	1			μs
RESET low-level width	trsl			10			μs

Remark fMCK: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))

Minimum Instruction Execution Time During Main System Clock Operation

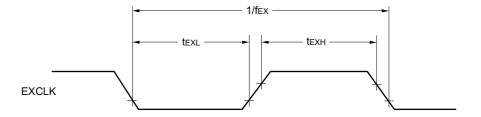
Tcy vs Vdd



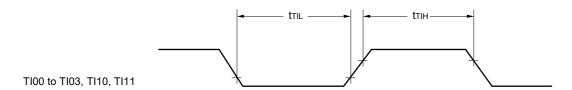
AC Timing Test Points

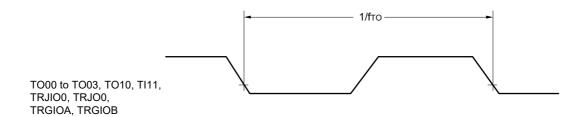


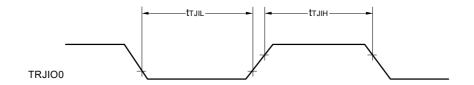
External System Clock Timing

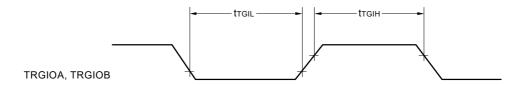


TI/TO Timing

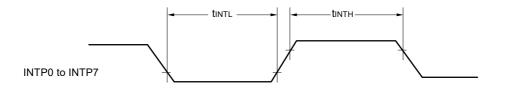




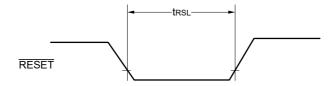




Interrupt Request Input Timing

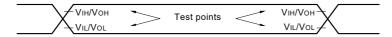


RESET Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	ed main) Mode	Unit
			MIN.	MAX.	
Transfer rate Note 1				fmck/12	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 2		2.6	Mbps

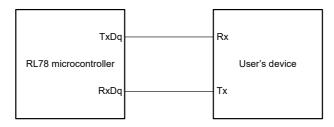
- Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.
- Note 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

32 MHz (2.7 V \leq VDD \leq 5.5 V)

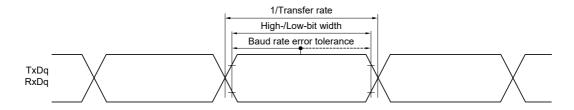
16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0, 1), g: PIM or POM number (g = 1)

 $\textbf{Remark 2.} \ \, \textbf{fmck: Serial array unit operation clock frequency}$

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03))

(2) During communication at same potential (Simplified SPI(CSI) mode) (master mode, SCKp... internal clock output)

(Ta = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions		` • .	S (high-speed main) mode	
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	250		ns
			$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	500		ns
SCKp high-/low-level width	tkh1, tkl1	4.0 V ≤ V _{DD} ≤ 5.5 V		tkcy1/2 - 24		ns
		2.7 V ≤ V _{DD} ≤ 5.5 V		tkcy1/2 - 36		ns
		$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$		tkcy1/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	tsiĸ1	4.0 V ≤ V _{DD} ≤ 5.5 V		66		ns
		2.7 V ≤ V _{DD} ≤	5.5 V	66		ns
		2.4 V ≤ V _{DD} ≤	5.5 V	113		ns
SIp hold time (from SCKp↑) Note 1	t KSI1			38		ns
Delay time from SCKp↓ to SOp output Note 2	tkso1	C = 30 pF Note	: 3		50	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKpţ" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. The SIp hold time becomes "from SCKpţ" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: Simplified SPI(CSI) number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM number (g = 1)
- Remark 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00, 01))

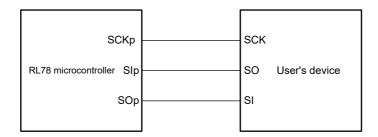
(3) During communication at same potential (Simplified SPI(CSI) mode) (slave mode, SCKp... external clock input)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

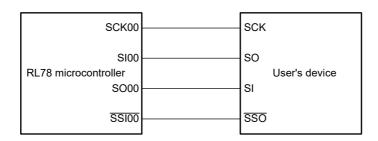
Parameter	Symbol	Conditions		HS (high-speed	Unit	
				MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	$4.0~V \leq V_{DD} \leq 5.5~V$	20 MHz < fмск	16/fмск		ns
			fмcк ≤ 20 MHz	12/fмск		ns
		$2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$	16 MHz < fмск	16/fмск		ns
			fмcк ≤ 16 MHz	12/fмск		ns
		$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$		12/fмск and 1000		ns
SCKp high-/low-level width	t кн2, t кL2	$4.0 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$		tkcy2/2 - 14		ns
		2.7 V ≤ V _{DD} ≤ 5.5 V		tkcy2/2 - 16		ns
		$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$	tkcy2/2 - 36		ns	
SIp setup time (to SCKp↑) Note 2	p setup time (to SCKp \uparrow) Note 2 t_{SIK2} 2.7 V \leq VD			1/fмск + 40		ns
		$2.4~V \leq V_{DD} \leq 5.5~V$		1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 2	t _{KSI2}			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output	tkso2	C = 30 pF Note 4	$2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$		2/fмск + 66	ns
Note 3			$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$		2/fмск + 113	ns
SSI00 setup time	tssıĸ	DAPmn = 0	$2.7~V \leq V_{DD} \leq 5.5~V$	240		ns
			$2.4~V \leq V_{DD} \leq 5.5~V$	400		ns
		DAPmn = 1	$2.7~V \leq V_{DD} \leq 5.5~V$	1/fмск + 240		ns
			$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	1/fmck + 400		ns
SSI00 hold time	tkssi	DAPmn = 0	$2.7~V \leq V_{DD} \leq 5.5~V$	1/fмск + 240		ns
			$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	1/fmck + 400		ns
		DAPmn = 1	$2.7~V \leq V_{DD} \leq 5.5~V$	240		ns
			$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	400		ns

- **Note 1.** The maximum transfer rate in the SNOOZE mode is 1 Mbps.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **Note 4.** C is the load capacitance of the SOp output lines.
- Caution Select the normal input buffer for the SIp and SCKp pins and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: Simplified SPI(CSI) number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM number (g = 1)
- Remark 2. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, $% \left(\frac{1}{2}\right) =\frac{1}{2}\left(\frac{1}{2}\right) =$
 - n: Channel number (mn = 00, 01))

Simplified SPI(CSI) mode connection diagram (during communication at same potential)



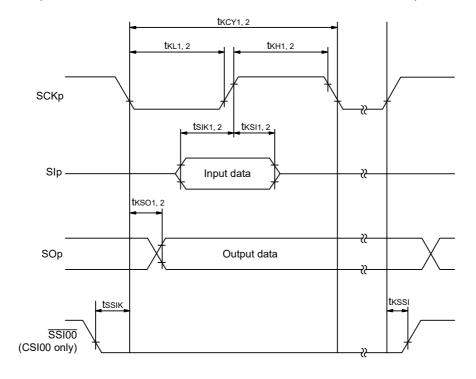
Simplified SPI(CSI) mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))



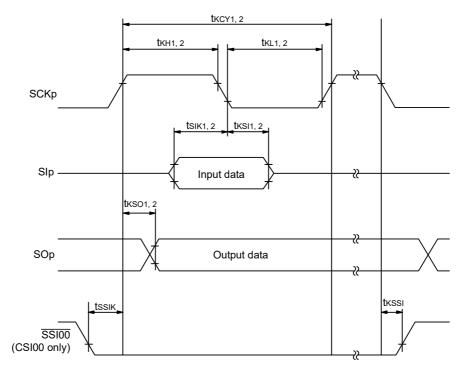
Remark 1. p: Simplified SPI(CSI) number (p = 00, 01)

Remark 2. m: Unit number, n: Channel number (mn = 00, 01)

Simplified SPI(CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI(CSI) mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: Simplified SPI(CSI) number (p = 00, 01)

Remark 2. m: Unit number, n: Channel number (mn = 00, 01)

(4) During communication at same potential (simplified I²C mode)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	d main) mode	Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega$		400 Note 1	kHz
		$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF, } R_b = 3 \text{ k}\Omega$		100 Note 1	kHz
Hold time when SCLr = "L"	tLow	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega$	1200		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF, } R_{\text{b}} = 3 \text{ k}\Omega$	4600		ns
Hold time when SCLr = "H"	thigh	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega$	1200		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF, } R_{\text{b}} = 3 \text{ k}\Omega$	4600		ns
Data setup time (reception)	tsu: dat	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1/f _{MCK} + 220 Note 2		ns
		$2.4~V \leq V_{DD} \leq 5.5~V,$ $C_b = 100~pF,~R_b = 3~k\Omega$	1/f _{MCK} + 580 Note 2		ns
Data hold time (transmission)	thd: dat	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega$	0	770	ns
		$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF, } R_b = 3 \text{ k}\Omega$	0	1420	ns

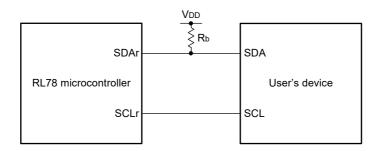
Note 1. The value must also be equal to or less than fmck/4.

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

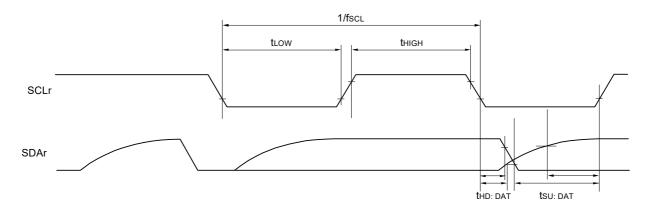
(Remarks are listed on the next page.)

Note 2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



 $\textbf{Remark 1.} \ \ \mathsf{Rb} \ [\Omega] : \textbf{Communication line (SDAr) pull-up resistance, Cb} \ [F] : \textbf{Communication line (SDAr, SCLr) load capacitance}$

Remark 2. r: IIC number (r = 00, 01), g: PIM number (g = 1), h: POM number (h = 1)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0),

n: Channel number (n = 0, 1), mn = 00, 01)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(1/2)

Parameter	Symbol		Conditions	, •	HS (high-speed main) mode	
				MIN.	MAX.	
Transfer rate		Reception	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$		f _{MCK} /12 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 2		2.6	Mbps
		-	$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		f _{MCK} /12 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 2		2.6	Mbps
		-	$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$		f _{MCK} /12 Note 1	bps
			Theoretical value of the maximum transfer rate fmck = fclk Note 2		2.6	Mbps

- Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.
- Note 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

32 MHz (2.7 V \leq VDD \leq 5.5 V) 16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- Remark 1. Vb [V]: Communication line voltage
- Remark 2. q: UART number (q = 0, 1), g: PIM or POM number (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00, 01)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

(2/2)

Parameter	Symbol		Conditions	HS (high-speed main) mode		Unit
				MIN.	MAX.	
Transfer rate		Transmission	$4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V$		Note 1	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF, } R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.6 Note 2	Mbps
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		Note 3	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{k}\Omega, V_b = 2.3 \text{V}$		1.2 Note 4	Mbps
			$2.4 \text{ V} \le \text{V}_{\text{DD}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$		Note 5	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$		0.43 Note 6	Mbps

Note 1. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq VDD \leq 5.5 V and 2.7 V \leq Vb \leq 4.0 V

Note 2. This value as an example is calculated when the conditions described in the "Conditions" column are met.

Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

$$\frac{1}{ \left\{ -C_b \times R_b \times \ln\left(1 - \frac{2.0}{V_b}\right) \right\} \times 3} [bps]$$
 Baud rate error (theoretical value) =
$$\frac{\frac{1}{Transfer\ rate \times 2} - \left\{ -C_b \times R_b \times \ln\left(1 - \frac{2.0}{V_b}\right) \right\}}{\left(\frac{1}{Transfer\ rate}\right) \times \text{Number of transferred bits}}$$

Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met.

Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



^{*} This value is the theoretical value of the relative difference between the transmission and reception sides.

^{*} This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 5. The smaller maximum transfer rate derived by using fMCK/12 or the following expression is the valid maximum transfer rate

Expression for calculating the transfer rate when 2.4 V \leq VDD < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \text{In} (1 - \frac{1.5}{\text{Vb}})\} }{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

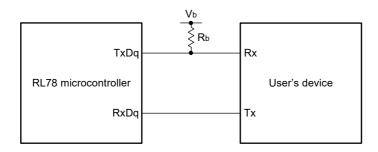
- Note 6. This value as an example is calculated when the conditions described in the "Conditions" column are met.

 Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

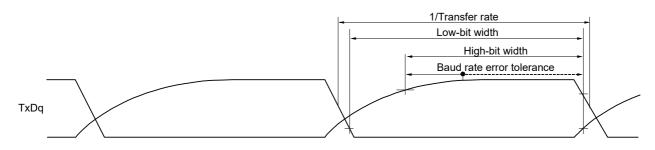
(Remarks are listed on the next page.)

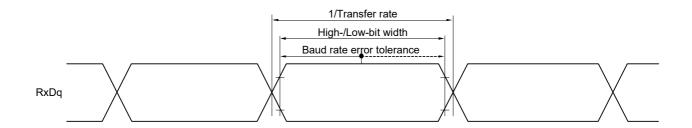
^{*} This value is the theoretical value of the relative difference between the transmission and reception sides.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remark 1.** Rb $[\Omega]$: Communication line (TxDq) pull-up resistance,
 - Cb [F]: Communication line (TxDq) load capacitance, Vb [V]: Communication line voltage
- Remark 2. q: UART number (q = 0, 1), g: PIM or POM number (g = 1)
- Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00, 01))

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI(CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(1/3)

Parameter	Symbol		Conditions	HS (high-speed	I main) mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	$t_{\text{KCY1}} \qquad t_{\text{KCY1}} \geq 4/f_{\text{CLK}} \qquad 4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF, } R_{\text{b}} = 1.4 \text{ k}\Omega$		600		ns
			$2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V},$ $C_{b} = 30 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$		ns	
			$2.4 \ V \le V_{DD} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V,$ $C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$	2300		ns
SCKp high-level width tkh1		$ 4.0 \ V \le V_{DD} \le 5.5 \ V, $ $ 2.7 \ V \le V_b \le 4.0 \ V, $ $ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega $		tксу1/2 - 150		ns
		$\begin{split} 2.7 & \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF, } R_{\text{b}} = 2.7 \text{ k}\Omega \end{split}$		tксү1/2 - 340		ns
		$ 2.4 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V}, \\ C_{b} = 30 \text{ pF}, R_{b} = 5.5 \text{ k}\Omega $		tксү1/2 - 916		ns
SCKp low-level width tkl1		$ \begin{aligned} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_{b} \leq 4.0 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 1.4 \ k\Omega \end{aligned} $		tксү1/2 - 24		ns
		2.3 V ≤ V _b ≤ 2	$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$ $C_{b} = 30 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$			ns
		$2.4 \text{ V} \le \text{V}_{DD} <$ $1.6 \text{ V} \le \text{V}_{b} \le 2$ $C_{b} = 30 \text{ pF, Re}$.0 V,	tксу1/2 - 100		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI(CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(2/3)

Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) ^{Note}	tsıĸı	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} & = 30 \text{ pF}, \text{ R}_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$	162		ns
		$\begin{split} 2.7 & \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 30 \text{ pF}, \text{ R}_{b} = 2.7 \text{ k}\Omega \end{split}$	354		ns
		$\label{eq:controller} \begin{split} 2.4 & \ V \leq V_{DD} < 3.3 \ V, \\ 1.6 & \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	958		ns
SIp hold time (from SCKp↑) ^{Note}	tksıı	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ C_b &= 30 \text{ pF, } R_b = 1.4 \text{ k}\Omega \end{aligned}$	38		ns
		$\label{eq:controller} \begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 2.7 \ k\Omega \end{split}$	38		ns
		$\label{eq:controller} \begin{split} 2.4 & \ V \leq V_{DD} < 3.3 \ V, \\ 1.6 & \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	38		ns
Delay time from SCKp↓ to SOp output ^{Note}	tkso1	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$		200	ns
		$\begin{split} 2.7 & \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega \end{split}$		390	ns
		$\label{eq:controller} \begin{split} 2.4 \ V &\leq V_{DD} < 3.3 \ V, \\ 1.6 \ V &\leq V_{b} \leq 2.0 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 5.5 \ k \Omega \end{split}$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI(CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(3/3)

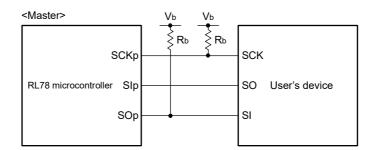
Parameter	Symbol	Conditions	HS (high-spee	high-speed main) mode	
			MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note}	tsıĸı	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$	88		ns
		$\begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 2.7 \ k \Omega \end{split}$	88		ns
		$2.4 \ V \leq V_{DD} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$	220		ns
SIp hold time (from SCKp↓) Note	tksi1	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} & = 30 \text{ pF}, \text{ R}_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$	38		ns
		$\label{eq:section_loss} \begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 2.7 \ k\Omega \end{split}$	38		ns
		$\label{eq:controller} \begin{split} 2.4 \ V &\leq V_{DD} < 3.3 \ V, \\ 1.6 \ V &\leq V_{b} \leq 2.0 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 5.5 \ k\Omega \end{split}$	38		ns
Delay time from SCKp↑ to SOp output ^{Note}	tkso1	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$		50	ns
		$\begin{split} 2.7 & \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega \end{split}$		50	ns
		$\label{eq:controller} \begin{split} 2.4 \ V &\leq V_{DD} < 3.3 \ V, \\ 1.6 \ V &\leq V_{b} \leq 2.0 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 5.5 \ k \Omega \end{split}$		50	ns

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

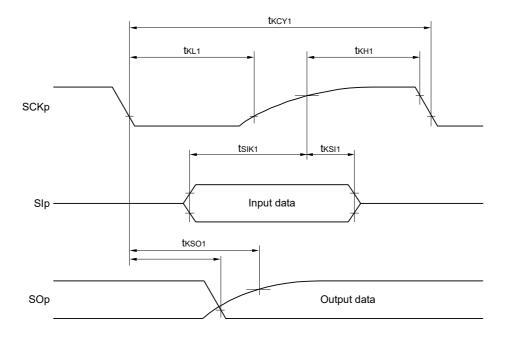
(Remarks are listed on the next page.)

Simplified SPI(CSI) mode connection diagram (during communication at different potential

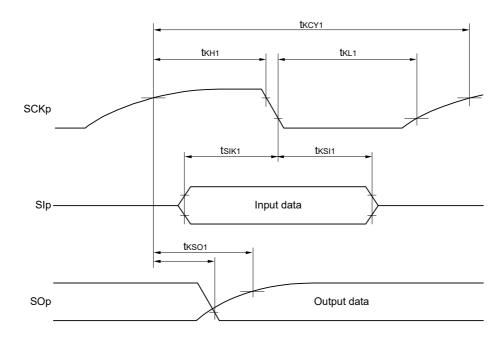


- Remark 1. Rb [Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb [F]: Communication line (SCKp, SOp) load capacitance, Vb [V]: Communication line voltage
- Remark 2. p: Simplified SPI(CSI) number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00, 01))

Simplified SPI(CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI(CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: Simplified SPI(CSI) number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI(CSI) mode) (slave mode, SCKp... external clock input)

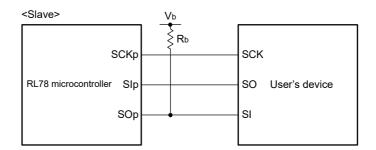
(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol	Co	nditions	HS (high-spee	ed main) mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	$4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V},$	24 MHz < fmck	28/fмск		ns
		$2.7~V \leq V_b \leq 4.0~V$	20 MHz < fмcк ≤ 24 MHz	24/fмск		ns
			8 MHz < fмск ≤ 20 MHz	20/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
	$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$	24 MHz < fmck	40/fмск		ns	
			20 MHz < fмcк ≤ 24 MHz	32/fмск		ns
			16 MHz < fмcк ≤ 20 MHz	28/fмск		ns
			8 MHz < fмск ≤ 16 MHz	24/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
	$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$	24 MHz < fmck	96/fмск		ns	
		$1.6~V \leq V_b \leq 2.0~V$	20 MHz < fмcк ≤ 24 MHz	72/fмск		ns
			16 MHz < fмcк ≤ 20 MHz	64/fмск		ns
			8 MHz < fмск ≤ 16 MHz	52/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	32/fмск		ns
			fмcк ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level	tkh2, tkl2	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, 2$	2.7 V ≤ V _b ≤ 4.0 V	tkcy2/2 - 24		ns
width		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}, 2$	$2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$	tkcy2/2 - 36		ns
		$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V}, 1$	$1.6~V \le V_b \le 2.0~V$	tkcy2/2 - 100		ns
SIp setup time	tsıĸ2	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, 2$	$2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$	1/f _{MCK} + 40		ns
(to SCKp↑) Note 2		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}, 2$	$2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$	1/fмск + 40		ns
		$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V}, 1$	$1.6~V \le V_b \le 2.0~V$	1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 2	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output Note 3	tkso2	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, 2$ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ I}$			2/fмск + 240	ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}, 2$ $C_b = 30 \text{ pF}, R_b = 2.7 \text{ I}$	·		2/f _{MCK} + 428	ns
		$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V}, 1$ $C_b = 30 \text{ pF}, R_b = 5.5$	·		2/fмск + 1146	ns

(Notes, Cautions, and Remarks are listed on the next page.)

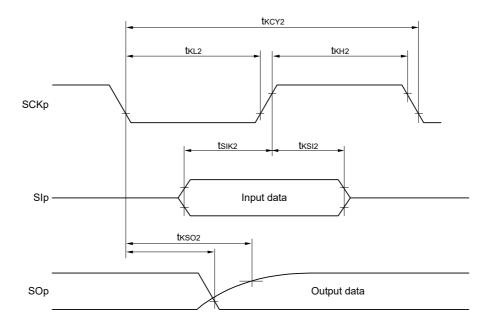
- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp and SCKp pins, and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Simplified SPI(CSI) mode connection diagram (during communication at different potential)

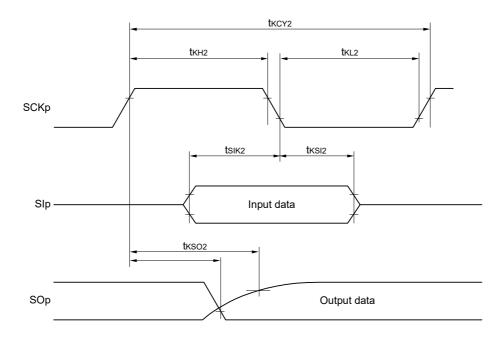


- **Remark 1.** Rb [Ω]: Communication line (SOp) pull-up resistance, Cb [F]: Communication line (SOp) load capacitance, Vb [V]: Communication line voltage
- Remark 2. p: Simplified SPI(CSI) number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00, 01))
- Remark 4. Communication at different potential cannot be performed during clocked serial communication with the slave select function.

Simplified SPI(CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI(CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: Simplified SPI(CSI) number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)

Remark 2. Communication at different potential cannot be performed during clocked serial communication with the slave select function.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(1/2)

Parameter	Symbol	Conditions	HS (high-spe	HS (high-speed main) mode		
			MIN.	MAX.		
SCLr clock frequency	fscL	$\begin{aligned} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$		400 Note 1	kHz	
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V},$ $C_{b} = 50 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$		400 Note 1	kHz	
		$ \begin{aligned} &4.0 \; \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \; \text{V}, \\ &2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ &C_{\text{b}} = 100 \; \text{pF}, \; R_{\text{b}} = 2.8 \; \text{k}\Omega \end{aligned} $		100 Note 1	kHz	
		$\label{eq:controller} \begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 100 \ pF, \ R_{b} = 2.7 \ k\Omega \end{split}$		100 Note 1	kHz	
		$2.4 \ V \leq V_{DD} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega$		100 Note 1	kHz	
Hold time when SCLr = "L"	tLOW	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V}, \\ C_{b} = 50 \text{ pF}, \text{ R}_{b} = 2.7 \text{ k}\Omega \end{aligned}$	1200		ns	
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V},$ $C_{b} = 50 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$	1200		ns	
		$ \begin{aligned} &4.0 \; \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \; \text{V}, \\ &2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ &C_{\text{b}} = 100 \; \text{pF}, \; R_{\text{b}} = 2.8 \; \text{k}\Omega \end{aligned} $	4600		ns	
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 100 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$	4600		ns	
		$2.4 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V}, \\ C_{b} = 100 \text{ pF}, R_{b} = 5.5 \text{ k}\Omega$	4600		ns	
Hold time when SCLr = "H"	tнісн	$\begin{aligned} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	620		ns	
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 50 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$	500		ns	
		$\begin{aligned} &4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned}$	2700		ns	
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 100 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$	2400		ns	
		$2.4 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V}, \\ C_{b} = 100 \text{ pF}, R_{b} = 5.5 \text{ k}\Omega$	1830		ns	

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(2/2)

Parameter	Symbol	Conditions	HS (high-speed m	nain) mode	Unit
			MIN.	MAX.	
Data setup time (reception)	tsu:dat	$ \begin{aligned} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	1/f _{MCK} + 340 Note 2		ns
		$\label{eq:controller} \begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1/f _{MCK} + 340 Note 2		ns
		$ \begin{aligned} &4.0 \; \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \; \text{V}, \\ &2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ &C_{\text{b}} = 100 \; \text{pF}, \; R_{\text{b}} = 2.8 \; \text{k}\Omega \end{aligned} $	1/f _{MCK} + 760 Note 2		ns
		$\label{eq:controller} \begin{split} 2.7 & \ V \le V_{DD} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1/f _{MCK} + 760 Note 2		ns
		$\label{eq:controller} \begin{split} 2.4 & \ V \leq V_{DD} < 3.3 \ V, \\ 1.6 & \ V \leq V_b \leq 2.0 \ V, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	1/f _{MCK} + 570 Note 2		ns
Data hold time (transmission)	thd:dat	$ \begin{aligned} 4.0 \ V &\leq V_{DD} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	0	770	ns
		$2.7 \ V \leq V_{DD} < 4.0 \ V,$ $2.3 \ V \leq V_b \leq 2.7 \ V,$ $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega$	0	770	ns
		$ \begin{aligned} &4.0 \; V \leq V_{DD} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	0	1420	ns
			0	1420	ns
		$\label{eq:section} \begin{split} 2.4 & \ V \le V_{DD} < 3.3 \ V, \\ 1.6 & \ V \le V_{b} \le 2.0 \ V, \\ C_{b} = 100 \ pF, \ R_{b} = 5.5 \ k\Omega \end{split}$	0	1215	ns

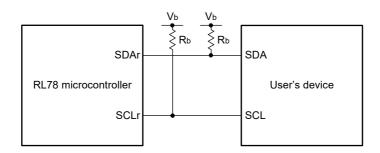
Note 1. The value must also be equal to or less than fmck/4.

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the N-ch open drain output (VDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

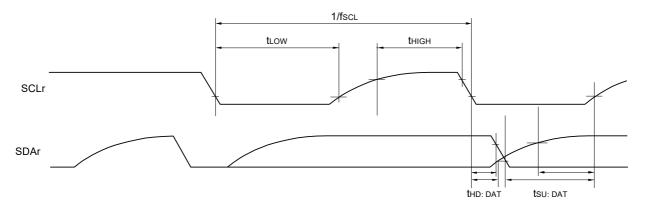
(Remarks are listed on the next page.)

Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- Remark 1. Rb $[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, Cb [F]: Communication line (SDAr, SCLr) load capacitance, Vb [V]: Communication line voltage
- Remark 2. r: IIC number (r = 00, 01), g: PIM, POM number (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0),

 n: Channel number (n = 0), mn = 00, 01)

2.6 Analog Characteristics

2.6.1 Programmable gain instrumentation amplifier and 24-bit $\Delta\Sigma$ A/D converter

(1) Analog input in differential input mode

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dofr = 0 mV, Vcom = 1.0 V, external clock input used)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Full-scale differential input voltage range	VID	VID = (PGAxP - PGAxN) (x = 0 to 3)		± 800 /Gtotal		mV
Input voltage range	VI	Each of PGAxP and PGAxN pins (x = 0 to 3)	0.2		1.8	V
Common mode input voltage	Vсом	dofr = 0 mV	0.2+(VID X GSET1)/2		1.8-(VID X GSET1)/2	V
Input bias current	lin	VI = 1.0 V			±50	nA
Input offset current	INOFR	VI = 1.0 V			±20	nA

(2) Analog input in single-ended input mode

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dofr = 0 mV, Vcom = 1.0 V, external clock input used)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage range	Vı	Each of PGAxP and PGAxN pins	0.2		1.8	V
		(x = 0 to 3)				
		GSET1 = 1, GSET2 = 1				
Input bias current	lin	VI = 1.0 V			±50	nA

(3) Programmable gain instrumentation amplifier and 24-bit $\Delta\Sigma$ A/D converter

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dofr = 0 mV, Vcom = 1.0 V, external clock input used, in differential input mode) (1/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES				24	bit
Sampling frequency	fs1	Normal mode		1		MHz
	fs2	Low power mode		0.125		MHz
Output data rate	fDATA1	Normal mode	0.48828		15.625	ksps
	fDATA2	Low power mode	61.03615		1953.125	sps
Gain setting range	GTOTAL	GTOTAL = GSET1 × GSET2	1		64	V/V
1st gain setting range	GSET1	In differential input mode only		1, 2, 3, 4, 8		V/V
2nd gain setting range	GSET2	In differential input mode only		1, 2, 4, 8		V/V
Offset adjustment bit range	dоггв			5		bit
Offset adjustment range	dofr	Referred to input	-164/GSET1		+164/GSET1	mV
Offset adjustment steps	dors	Referred to input		11/Gset1		mV

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dofr = 0 mV, Vcom = 1.0 V, external clock input used, in differential input mode) (2/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Gain error	Eg	TA = 25°C GSET1 = 1, GSET2 = 1 Excluding SBIAS error		±0.2	±2.7	%
		TA = 25°C GSET1 = 8, GSET2 = 4 Excluding SBIAS error		±0.1		%
Gain drift ^{Note}	dEg	GSET1 = 1, GSET2 = 1 Excluding SBIAS drift		(5.6)	(22.0)	ppm/°C
		GSET1 = 8, GSET2 = 4 Excluding SBIAS drift		(9.1)		ppm/°C
Offset error	Eos	TA = 25°C GSET1 = 1, GSET2 = 1 Referred to input		±0.32	±2.90	mV
		TA = 25°C GSET1 = 8, GSET2 = 4 Referred to input		±0.03		mV
Offset drift Note	dEos	GSET1 = 1, GSET2 = 1 Referred to input		(±0.02)	(±6.00)	μV/°C
		GSET1 = 8, GSET2 = 4 Referred to input		(±0.02)		μV/°C
SND ratio	SNDR	GSET1 = 1, GSET2 = 1, fiN = 50 Hz Normal mode, pin = -1 dBFS	(82)	(85)		dB
		GSET1 = 8, GSET2 = 4, fin = 50 Hz Normal mode, pin = -1 dBFS	(73)	(80)		dB
Noise	Vn	GSET1 = 1, GSET2 = 1, OSR = 2048		(13)		μVRms
		GSET1 = 8, GSET2 = 4, OSR = 2048		(0.6)		μVRms
Integral non-linearity error	INL	GSET1 = 1, GSET2 = 1, OSR = 2048		(±10)		ppmFS
Common mode rejection ratio	CMRR	VCOM = 1.0±0.8 V, fin = 50 Hz GSET1 = 1, GSET2 = 1 Differential input mode	(72)	(90)		dB
Power supply rejection ratio	PSRR	AVDD = 2.7 to 5.5 V GSET1 = 1, GSET2 = 1 Differential input mode		(85)		dB
$\Delta\Sigma$ A/D converter input clock frequency	fADC		3.8	4	4.2	MHz

Note Calculate the gain drift and offset drift by using the following expression (for 105°C products):

For gain drift: (MAX(Eg(T(-40) to T(105))) - MIN(Eg(T(-40) to T(105)))) / (105°C -(-40°C))

For offset drift: (MAX(Eos(T(-40) to T(105))) - MIN(Eos(T(-40) to T(105)))) / (105°C - (-40°C))

MAX(E_G(T₍₋₄₀₎ to T₍₁₀₅₎)): The maximum value of gain error when the temperature range is -40°C to 105°C MIN(E_G(T₍₋₄₀₎ to T₍₁₀₅₎)): The minimum value of gain error when the temperature range is -40°C to 105°C MAX(E_{OS}(T₍₋₄₀₎ to T₍₁₀₅₎)): The maximum value of offset error when the temperature range is -40°C to 105°C MIN(E_{OS}(T₍₋₄₀₎ to T₍₁₀₅₎)): The minimum value of offset error when the temperature range is -40°C to 105°C

Remark In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

2.6.2 Sensor power supply (SBIAS)

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, Cout = 0.22 μ F, Vout = 1.0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output voltage range	Vouт		0.5		2.2	V
Output voltage setting steps	VSTEP			0.1		V
Output voltage precision	VA	IOUT = 1 mA	(-3)		(+3)	%
Maximum output current	Іоит		5			mA
Short circuit current	ISHORT	Vout = 0 V		40	65	mA
Load regulation	LR	1 mA ≤ Iout ≤ 5 mA			(15)	mV
Power supply rejection ratio	PSRR	AVDD = 5.0 V + 0.1 Vpp ripple f = 100 Hz, Iout = 2.5 mA	(45)	(50)		dB

Remark In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

2.6.3 Temperature sensor

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature coefficient for sensor	TCsns			(756)		μV/°C
Sensor output voltage	VTEMP	TA = 25°C		226.4		mV

Remark In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

2.6.4 A/D converter characteristics

(1) When positive reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), negative reference voltage (-) = AVSS (ADREFM = 0), pins subject to A/D conversion: ANI0 to ANI9 and SBIAS

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = AVDD, negative reference voltage (-) = AVss)

Parameter	Symbol	Condition	ons	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$4.0 \text{ V} \leq \text{AV}_{DD} \leq 5.5 \text{ V}$		1.2	±6.5	LSB
		ANI0 to ANI9, SBIAS	$2.7 \text{ V} \leq \text{AV}_{DD} \leq 5.5 \text{ V}$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$4.0 \text{ V} \leq \text{AV}_{DD} \leq 5.5 \text{ V}$	2.125		39	μs
			$2.7 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$	3.1875		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	$4.0 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$			±0.50	%FSR
		ANI0 to ANI9, SBIAS	$2.7 \text{ V} \leq \text{AV}_{DD} \leq 5.5 \text{ V}$			±0.60	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	$4.0 \text{ V} \leq \text{AV}_{DD} \leq 5.5 \text{ V}$			±0.50	%FSR
		ANI0 to ANI9, SBIAS	$2.7 \text{ V} \leq \text{AV}_{\text{DD}} \leq 5.5 \text{ V}$			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$4.0 \text{ V} \leq \text{AV}_{DD} \leq 5.5 \text{ V}$			±3.5	LSB
		ANI0 to ANI9, SBIAS	$2.7 \text{ V} \leq \text{AV}_{DD} \leq 5.5 \text{ V}$			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.7 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$			±2.0	LSB
Analog input voltage	Vain	ANI0 to ANI9		AVss		AV _{DD}	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Caution The number of pins depends on the product. For details, see a list of pin functions.

(2) When positive reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), negative reference voltage (-) = AVss (ADREFM = 0), pins subject to A/D conversion: ANI0 to ANI9 and SBIAS

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = VBGR, negative reference voltage (-) = AVss)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	2.7 V ≤ AV _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	$2.7 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$			±0.60	%FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.7 \text{ V} \le \text{AV}_{DD} \le 5.5 \text{ V}$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	2.7 V ≤ AV _{DD} ≤ 5.5 V			±1.0	LSB
Internal reference voltage (+)	V _{BGR}	$2.7 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$		V _{BGR} Note 3		V	
Analog input voltage	Vain	ANI0 to ANI9	•	0		V _{BGR}	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. See the Internal reference voltage characteristics.

2.6.5 12-bit D/A converter

(1) When positive reference voltage (+) = AVDD (DACVRF = 0)

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = AVDD)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	DARES				(12)	bit
Output voltage range	DAOUT	12-bit resolution	0.35		AVDD-0.47	V
Integral non-linearity error	DAILE	12-bit resolution			±4.0	LSB
Differential non-linearity error	DADLE	12-bit resolution			±1.0	LSB
Offset error	DAErr	12-bit resolution			±30	mV
Gain error	DAEG	12-bit resolution			±20	mV
Settling time	DAtset	12-bit resolution, CL = 50 pF, RL = $10 \text{ k}\Omega$			(60)	μs

Remark 1. In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

Remark 2. The 12-bit D/A converter characteristics are the values obtained with the configurable amplifier connected.

(2) When positive reference voltage (+) = internal reference voltage (DACVRF = 1)

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = VREFDA)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	DARES				(8)	bit
Internal reference voltage	VREFDA	8-bit resolution	1.34	1.45	1.54	V
Output voltage range	DAOUT	8-bit resolution	0.35		VREFDA	V
Integral non-linearity error	DAILE	8-bit resolution			±1.0	LSB
Differential non-linearity	DADLE	8-bit resolution			±1.0	LSB
error						
Offset error	DAErr	8-bit resolution			±30	mV
Gain error	DAEG	8-bit resolution			±20	mV
Settling time	DAtset	8-bit resolution, CL = 50 pF, RL = 10 k Ω			(60)	μs

Remark 1. In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

Remark 2. The 12-bit D/A converter characteristics are the values obtained with the configurable amplifier connected.

Remark 3. Offset error and gain error do not include error in the internal reference voltage.

2.6.6 Configurable amplifier

(TA = -40 to +105°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, Vcom = 1/2 AVDD, internally connected voltage follower)

AMP0 configuration SW setting: Positive (+) pin = ANX1, negative (-) pin = ANX0 AMP1 configuration SW setting: Positive (+) pin = ANX3, negative (-) pin = ANX2 AMP2 configuration SW setting: Positive (+) pin = ANX5, negative (-) pin = ANX4

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage	Vin		AVss		AVDD	V
Output voltage	Vol	IL= -1 mA, AV _{DD} = 2.7 to 5.5 V		AVss +0.02	AVss +0.07	V
	Vон	IL= 1 mA, AV _{DD} = 2.7 to 5.5 V	AV _{DD} -0.15	AV _{DD} -0.02		V
Maximum output current	Іоит	4.5 V ≤ AVDD ≤ 5.5 V	±10			mA
		2.7 V ≤ AVDD ≤ 5.5 V	±5			mA
Input-referred offset voltage	Voff	TA = 25°C without trimming IL = 0 mA, VCOM = 1.0 V		±1	±4	mV
		TA = 25°C with trimming IL = 0 mA, VCOM = 1.0 V			±0.35	mV
Temperature coefficient for inputreferred offset voltage	Vотс	IL = 0 mA		(±2)	(±8)	μV/°C
Slew rate	SR1	Normal mode $C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega$		(0.1)		V/µs
	SR2	High-speed mode $C_L = 50$ pF, $R_L = 10$ kΩ		(8.0)		V/µs
Gain bandwidth	GBW1	Normal mode $C_L = 50$ pF, $R_L = 10$ k Ω		(350)		kHz
	GBW2	High-speed mode $C_L = 50$ pF, $R_L = 10$ kΩ		(1.8)		MHz
Phase margin	θМ1	Normal mode $C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega$		(70)		deg
	θМ2	High-speed mode $C_L = 50$ pF, $R_L = 10$ kΩ		(60)		deg
Settling time	tset1	Normal mode $C_L = 50$ pF, $R_L = 10$ k Ω		(20)		μs
	tset2	High-speed mode $C_L = 50$ pF, $R_L = 10$ kΩ		(10)		μs
Peak-to-peak voltage noise	Enb	0.1 to 10 Hz Normal mode CL = 50 pF, RL = 10 kΩ		(2.0)		μVrms
Input-referred noise	En	f = 1 kHz, Normal mode CL = 50 pF, RL = 10 kΩ		(70)		nV/√Hz
Common mode rejection ratio	CMRR	$f = 1 \text{ kHz}$, $CL = 50 \text{ pF}$, $RL = 10 \text{ k}\Omega$		(70)		dB
Power supply rejection ratio	PSRR	$2.7 \text{ V} \le \text{AVdd} \le 5.5 \text{ V}$ f = 1 kHz, CL = 50 pF, RL = 10 k Ω		(62)		dB

(Remarks are listed on the next page.)



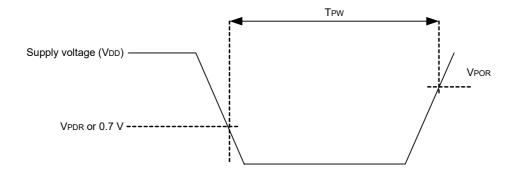
- Remark 1. In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.
- **Remark 2.** The TYP. conditions are the conditions when $T_A = 25^{\circ}C$ and AVDD = 5.0 V.
- Remark 3. Unless otherwise specified, offset trimming has proceeded.
- Remark 4. Unless otherwise specified, values are for operation in normal mode.

2.6.7 POR characteristics

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power on/down reset threshold	VPOR	Voltage threshold on VDD rising	1.48	1.56	1.62	V
	VPDR	Voltage threshold on VDD falling Note 1	1.47	1.55	1.61	V
Minimum pulse width Note 2	Tpw		300			μs

- **Note 1.** However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 2.4 AC Characteristics.
- Note 2. Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.8 LVD characteristics

(1) LVD detection voltage in reset mode and interrupt mode

(Ta = -40 to +105°C, VPDR \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Pa	rameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Voltage detection	Supply voltage level	VLVD0	Rising edge	4.62	4.74	4.84	V
threshold			Falling edge	4.52	4.64	4.74	V
		VLVD1	Rising edge	4.50	4.62	4.72	V
			Falling edge	4.40	4.52	4.62	V
		VLVD2	Rising edge	4.30	4.42	4.51	V
			Falling edge	4.21	4.32	4.41	V
		VLVD3	Rising edge	3.13	3.22	3.29	V
			Falling edge	3.07	3.15	3.22	V
		VLVD4	Rising edge	2.95	3.02	3.09	V
			Falling edge	2.89	2.96	3.02	V
		VLVD5	Rising edge	2.74	2.81	2.87	V
			Falling edge	2.68	2.75	2.81	V
		VLVD6	Rising edge	2.55	2.61	2.67	V
			Falling edge	2.49	2.55	2.61	V
Minimum pulse wid	dth	tLW		300			μs
Detection delay tim	пе					300	μs

(2) LVD detection voltage in interrupt & reset mode

(TA = -40 to +105°C, VPDR \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol		Condi	tions	MIN.	TYP.	MAX.	Unit
Voltage detection	VLVDD6	VPOC2,	VPOC1, VPOC0 = 0, 0, 0, fall	ing reset voltage	2.49	2.55	2.61	V
threshold	VLVDD4		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.95	3.02	3.09	V
				Falling interrupt voltage	2.89	2.96	3.02	V
	VLVDD3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.13	3.22	3.29	V
				Falling interrupt voltage	3.07	3.15	3.22	V
	VLVDD5	VPOC2,	VPOC1, VPOC0 = 0, 0, 1, fall	VPOC1, VPOC0 = 0, 0, 1, falling reset voltage		2.75	2.81	V
	VLVDD2		LVIS1, LVIS0 = 0, 0 Rising release reset voltage		4.30	4.42	4.51	V
				Falling interrupt voltage	4.21	4.32	4.41	V
	VLVDD5	VPOC2,	VPOC1, VPOC0 = 0, 1, 0, fall	ing reset voltage	2.68	2.75	2.81	V
	VLVDD1		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	4.50	4.62	4.72	V
				Falling interrupt voltage	4.40	4.52	4.62	V
	VLVDD5	VPOC2,	VPOC1, VPOC0 = 0, 1, 1, fall	ing reset voltage	2.68	2.75	2.81	V
	VLVDD3		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	3.13	3.22	3.29	V
				Falling interrupt voltage	3.07	3.15	3.22	V
	VLVDD0		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	4.62	4.74	4.84	V
				Falling interrupt voltage	4.52	4.64	4.74	V

2.6.9 Power supply voltage rising slope characteristics

$(TA = -40 \text{ to } +105^{\circ}C, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				50	V/ms

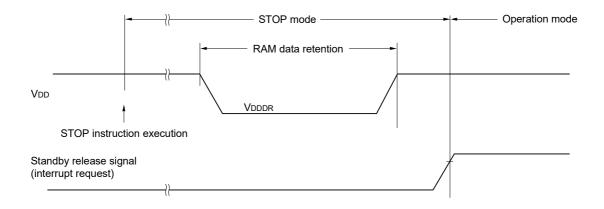
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

$(TA = -40 \text{ to } +105^{\circ}C, Vss = 0 \text{ V}))$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.47 Notes 1, 2		5.5	V

- **Note 1.** The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.
- Note 2. Enter STOP mode before the supply voltage falls below the recommended operating voltage.



2.8 Flash Memory Programming Characteristics

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	2.4 V ≤ VDD ≤ 5.5 V	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°CNote 4	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°CNote 4		1,000,000		
		Retained for 5 years TA = 85°CNote 4	100,000			
		Retained for 20 years TA = 85°CNote 4	10,000			

- Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
- Note 2. When using flash memory programmer and Renesas Electronics self-programming library
- **Note 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
- **Note 4.** This temperature is the average value at which data are retained.



2.9 Dedicated Flash Memory Programmer Communication (UART)

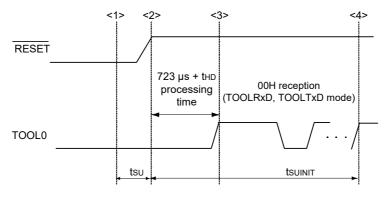
(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

2.10 Timing for Switching Flash Memory Programming Modes

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	thD	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends thD: How long to keep the TOOL0 pin at the low level from when the external resets end

(excluding the processing time of the firmware to control the flash memory)

3. ELECTRICAL SPECIFICATIONS (M: TA = -40 to +125°C)

This chapter describes the electrical specifications for the products "M: Industrial applications (TA = -40 to +125°C)".

- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Alternate functions other than AFE in the RL78/I1E User's Manual.
- Caution 3. Please contact Renesas Electronics sales office for derating of operation under TA = +85 to +125°C.

 Derating is the systematic reduction of load for the sake of improved reliability.
- **Remark** The electrical characteristics of the products M: Industrial applications (TA = -40 to +125°C) are different from those of the products "G: Industrial applications". For details, refer to **3.1** to **3.10**.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings

(1/2)

Parameter	Symbol	Cond	litions	Ratings	Unit
Supply voltage	VDD			-0.5 to +6.5	V
	AVDD	AVDD = VDD		-0.5 to +6.5	V
	AVss	AVss = Vss		-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC		-0.3 to +2.8	V
				and -0.3 to V _{DD} + 0.3 ^{Note 1}	
REGA pin input voltage	VIREGA	REGA		-0.3 to +2.8	
				and -0.3 to AV _{DD} + 0.3 Note 2	
Input voltage	Vıı	P10 to P15, P40, P121 RESET	, P122, P137, EXCLK,	-0.3 to V _{DD} +0.3 Note 3	V
Alternate-function pin	Vı2	P16, P17, P41, P42	Digital input voltage	-0.3 to V _{DD} + 0.3 Note 3	V
input voltage		(36-pin products only)	Analog input voltage	-0.3 to AV _{DD} + 0.3 Note 3	V
Analog input voltage	VIA	PGA0P to PGA3P, PGANIO to ANIO to ANIO to ANIO to ANIO to	,	-0.3 to AV _{DD} + 0.3 Note 3	V
Output voltage	Vo1	P10 to P15, P40		-0.3 to V _{DD} + 0.3 Note 3	V
Alternate-function pin	Vo2	P16, P17, P41, P42	Digital output voltage	-0.3 to V _{DD} + 0.3 Note 3	V
output voltage		(36-pin products only)	Analog output voltage	-0.3 to AV _{DD} + 0.3 Note 3	V
Analog output voltage	Voa	SBIAS, AMP0O to AMF	P2O, ANX0 to ANX5	-0.3 to AV _{DD} + 0.3 Note 3	V

- Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
- **Note 2.** Connect the REGA pin to AVss via a capacitor (0.22 μ F). This value regulates the absolute maximum rating of the REGA pin. Do not use this pin with voltage applied to it.
- Note 3. Must be 6.5 V or lower.
- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

 That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. Vss is used as the reference voltage.

Absolute Maximum Ratings

(2/2)

Parameter	Symbol		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P10 to P17, P40 to P42	-40	mA
		Total of all pins	P10 to P17, P41, P42 Note	-100	mA
Analog output current,	Іона	Per pin	AMP0O to AMP2O	-12	mA
high			ANX0 to ANX5	-0.12	mA
		Total of all pins	AMP0O to AMP2O, ANX0 to ANX5	-18	mA
Output current, low	IOL1	Per pin	P10 to P17, P40 to P42	40	mA
		Total of all pins	P10 to P17, P41, P42 Note	100	mA
Analog output current, low	IOLA	Per pin	AMP0O to AMP2O	12	mA
			ANX0 to ANX5	0.12	mA
		Total of all pins	AMP0O to AMP2O, ANX0 to ANX5	18	mA
Operating ambient	ТА	In normal operation	on mode	-40 to +125	°C
temperature		In flash memory p			
Storage temperature	Tstg			-65 to +150	°C

Note This indicates the total current value when P16, P17, P41, and P42 are used as digital input pins.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

Remark 2. Vss is used as the reference voltage.

3.2 Oscillator Characteristics

3.2.1 X1 characteristics

 $(TA = -40 \text{ to } +125^{\circ}\text{C}, 2.4 \text{ V} \le \text{AVDD} = \text{VDD} \le 5.5 \text{ V}, \text{AVss} = \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	1.0		20.0	MHz
	crystal resonator	$2.4 \text{ V} \leq \text{Vdd} < 2.7 \text{ V}$	1.0		16.0	

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time.

Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user.

Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator, refer to **5.4 System Clock Oscillator** in the RL78/I1E User's Manual..

3.2.2 On-chip oscillator characteristics

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency	fıн	2.7 V ≤ VDD ≤ 5.5 V	1		24	MHz
Notes 1, 2		2.4 V ≤ V _{DD} < 2.7 V	1		16	MHz
High-speed on-chip oscillator clock frequency		-40 to +105°C	-2.0		+2.0	%
accuracy		+105 to +125°C	-3.0		+3.0	%
Low-speed on-chip oscillator clock frequency	fı∟			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 3 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

3.2.3 PLL characteristics

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
PLL output frequencyNotes 1, 2,	fPLL	fmx = 8 MHz	DSFRDIV = 0	DSCM = 0		48		MHz
3			DSFRDIV = 1	DSCM = 0		24		MHz
				DSCM = 1		32		MHz
		fmx = 4 MHz	DSFRDIV = 0	DSCM = 0		24		MHz
				DSCM = 1		32		MHz
Lockup wait time			Fime from when PLL output is enabled to when the phase is locked					μs
Interval wait time			en the PLL stops op PLL operation is s	perating to when the pecified	4			μs
Setup wait time		•		input clock stabilizes to when the PLL is	1			μs

- Note 1. When using a PLL, input a clock of 4 MHz or 8 MHz to the PLL.
- **Note 2.** Be sure to specify one of these settings when using a PLL.
- Note 3. When using the PLL output as the CPU clock, fill is divided by 2, 4, or 8 according to the setting of the RDIV1 and RDIV0 bits

3.3 DC Characteristics

3.3.1 Pin characteristics

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

(1/3)

Item	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P10 to P17 and P40 to	$4.0 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			-3.0 Note 3	mA
		P42 Note 2	2.4 V ≤ V _{DD} < 4.0 V			-1.0 Note 3	mA
		, , ,	$4.0 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			-30.0	mA
		Note 3	2.7 V ≤ V _{DD} < 4.0 V			-19.0	mA
		(When duty ≤ 70% Note 4)	2.4 V ≤ V _{DD} < 2.7 V			-10.0	mA
Output current, low Note 1	IOL1	DAO Noto 2	$4.0 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			8.5 Note 3	mA
			2.7 V ≤ V _{DD} < 4.0 V			1.5 Note 3	mA
			2.4 V ≤ V _{DD} < 2.7 V			0.6 Note 3	mA
		Total of P10 to P17, P41, and P42	$4.0 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			40.0	mA
		Note 2	2.7 V ≤ V _{DD} < 4.0 V			35.0	mA
		(When duty ≤ 70% Note 4)	2.4 V ≤ V _{DD} < 2.7 V			20.0	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin.
- **Note 2.** This indicates the total current value when P16, P17, P41, and P42 are used as digital I/O ports. When using these pins as analog function (AFE) pins, refer to **3.1 Absolute Maximum Ratings**.
- Note 3. Do not exceed the total current value.
- **Note 4.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IOH × 0.7)/(n × 0.01)

Example: n = 80% when loh = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Caution P10 to P15 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(Ta = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

(2/3)

Item	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P10 to P17 and P40 to P42	Normal input buffer	0.8 VDD		VDD	V
	VIH2	P11, P12, P14,	TTL input buffer, $4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	2.2		VDD	V
		P15	TTL input buffer, 3.3 V ≤ V _{DD} < 4.0 V	2.0		VDD	V
			TTL input buffer, 2.4 V ≤ V _{DD} < 3.3 V	1.28		VDD	V
	VIH3	P121, P122, P13	7, EXCLK, RESET	0.8 Vdd		VDD	V
Input voltage, low	VIL1	P10 to P17 and P40 to P42	Normal input buffer	0		0.2 Vdd	V
		P11, P12, P14,	TTL input buffer, $4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0		0.8	V
		P15	TTL input buffer, 3.3 V ≤ V _{DD} < 4.0 V	0		0.5	V
			TTL input buffer, 2.4 V ≤ V _{DD} < 3.3 V	0		0.32	V
	VIL3	P121, P122, P13	7, EXCLK, RESET	0		0.2 Vdd	V
Output voltage, high	Vон1	P10 to P17 and	4.0 V ≤ V _{DD} ≤ 5.5 V, I _{OH1} = -3.0 mA	VDD - 0.7			V
		P40 to P42	2.4 V ≤ VDD ≤ 5.5 V, IOH1 = -1.0 mA	VDD - 0.5			V
Output voltage, low	VOL1	P10 to P17 and	$4.0 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{ IOL1} = 8.5 \text{ mA}$			0.7	V
		P40 to P42	2.7 V ≤ VDD ≤ 5.5 V, IOL1 = 1.5 mA			0.5	V
			$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}, \text{ lol1} = 0.6 \text{ mA}$			0.4	V

Caution The maximum V $_{\rm IH}$ value on P10 to P15 is V $_{\rm DD}$, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(Ta = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

(3/3)

Item	Symbol	Conditi	ons		MIN.	TYP.	MAX.	Unit
Input leakage	ILIH1	P10 to P17, and P40 to P42	Vı = Vdd				1	μΑ
current, high	ILIH2	P137, RESET	VI = VDD				1	μΑ
	Ішн3	P121, P122 (X1, X2, EXCLK)		In input port mode or when using external clock input			1	μА
				When a resonator is connected			10	μА
Input leakage	ILIL1	P10 to P17, and P40 to P42	Vı = Vss				-1	μΑ
current, low	ILIL2	P137, RESET	Vı = Vss				-1	μΑ
	ILIL3	P121, P122 (X1, X2, EXCLK)	Vı = Vss	In input port mode or when using external clock input When a resonator			-1 -10	μA μA
				is connected				
On-chip pull-up resistance	Rυ	P10 to P15, P40	Vı = Vss, ir	n input port mode	10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.3.2 Supply current characteristics

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(1/2)

Parameter	Symbol		Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	fHOCO = 24 MHz, fMAIN = 24 MHz Note 3	Basic	V _{DD} = 5.0 V		1.7		mA
current Note 1		mode ^{Note 2}		operation	V _{DD} = 3.0 V		1.7		
Note 1			fhoco = 24 MHz, fmain = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		3.8	7.6	mA
				operation	V _{DD} = 3.0 V		3.8	7.6	
			fhoco = 16 MHz, fmain = 16 MHz Note 3	Normal	V _{DD} = 5.0 V		2.8	5.6	
					V _{DD} = 3.0 V		2.8	5.6	
		fmx = 20 MHz, fmain = 20 MHz Note 4,	Normal	Square wave input		3.3	6.5	mA	
		$V_{DD} = 5.0 \text{ V}$ opera	operation	Resonator connection		3.5	6.6		
		f _{MX} = 20 MHz, f _{MAIN} = 20 MHz Note 4, Normal	Square wave input		3.3	6.5			
			V _{DD} = 3.0 V	operation	Resonator connection		3.5	6.6	
			fmx = 10 MHz, fmain = 10 MHz Note 4,	Normal	Square wave input		2.0	3.9	
			V _{DD} = 5.0 V	operation	Resonator connection		2.1	4.0	
			fmx = 10 MHz, fmain = 10 MHz Note 4,	Normal	Square wave input		2.0	3.9	
			V _{DD} = 3.0 V	operation	Resonator connection		2.1	4.0	
		fmx = 8 MHz, fmain = 24 MHz Note 5,	Normal	Square wave input		5.1	10.4	mA	
		$V_{DD} = 5.0 \text{ V}$ $f_{MX} = 8 \text{ MHz}, f_{MAIN} = 24 \text{ MHz} \text{ Note 5},$		operation	Resonator connection		5.2	10.5	
				Normal	Square wave input		5.1	10.4	
			V _{DD} = 3.0 V	operation	Resonator connection		5.2	10.5	

- Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the RTC, interval timer, watchdog timer, LVD circuit, AFE, I/O ports, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. The relationship between the operation voltage range and the CPU operating frequency is as below.

 $2.7~V \leq V_{DD} \leq 5.5~V$ @ 1 MHz to 24 MHz

2.4 V \leq VDD \leq 5.5 V @ 1 MHz to 16 MHz

- Note 3. When the high-speed system clock is stopped
- Note 4. When the high-speed on-chip oscillator and the PLL are stopped
- Note 5. When the high-speed on-chip oscillator is stopped and the PLL is operating
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency
- Remark 3. fmain: Main system clock frequency
- Remark 4. The temperature condition for the TYP. value is TA = 25°C

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

(2/2)

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Supply current	IDD2	HALT mode	fhoco = 24 MHz, fmain = 24 MHz Note 4	V _{DD} = 5.0 V		0.44	3.42	mA
Note 1	Note 2	Note 3		V _{DD} = 3.0 V		0.44	3.42	
			fhoco = 16 MHz, fmain = 16 MHz Note 4	V _{DD} = 5.0 V		0.40	2.50	
				V _{DD} = 3.0 V		0.40	2.50	
			fmx = 20 MHz, fmain = 20 MHz Note 5, VDD = 5.0 V	Square wave input		0.28	2.94	mA
				Resonator connection		0.49	3.08	
			fmx = 20 MHz, fmain = 20 MHz Note 5, VDD = 3.0 V	Square wave input		0.28	2.94	
				Resonator connection		0.49	3.08	
			fmx = 10 MHz, fmain = 10 MHz Note 5, VDD = 5.0 V	Square wave input		0.19	1.54	
				Resonator connection		0.30	1.63	
		f_{MX} = 10 MHz, f_{MAIN} = 10 MHz $^{Note 5}$, V_{DD} = 3.0 V	Square wave input		0.19	1.54		
			Resonator connection		0.30	1.63		
			fmx = 8 MHz, fmain = 24 MHz Note 6, VDD = 5.0 V	Square wave input		0.76	3.92	mA
				Resonator connection		0.86	4.04	
			fmx = 8 MHz, fmain = 24 MHz Note 6, VDD = 3.0 V	Square wave input		0.76	3.92	
				Resonator connection		0.86	4.04	
	IDD3	STOP mode	T _A = -40°C			0.38	1.14	μΑ
	Note 7		T _A = +25°C			0.50	1.14	
			T _A = +50°C			0.66	4.52	
			T _A = +70°C			1.04	7.98	
		T _A = +85°C			2.92	16.0		
			T _A = +105°C			11.0	100.0	
			T _A = +125°C			22.0	200.0	

- Note 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the RTC, interval timer, watchdog timer, LVD circuit, AFE, I/O ports, and on-chip pull-up/pull-down resistors and the current flowing during writing to the data flash.
- Note 2. During HALT instruction execution from flash memory
- Note 3. The relationship between the operation voltage range and the CPU operating frequency is as below. $2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V} \textcircled{2} 1 \text{ MHz}$ to 24 MHz
 - $2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$ @ 1 MHz to 16 MHz
- Note 4. When the high-speed system clock is stopped
- Note 5. When the high-speed on-chip oscillator and the PLL are stopped
- Note 6. When high-speed on-chip oscillator is stopped and the PLL is operating
- Note 7. The MAX. value includes the leakage current in STOP mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency
- Remark 3. fmain: Main system clock frequency
- Remark 4. The temperature condition for the TYP. value is TA = 25°C, except the operation in STOP mode.

· Peripheral functions

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol	Condit	ions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I _{FIL} Note 1				0.20		μА
RTC operating current	I _{RTC} Notes 1, 2, 3	fmx = 4 MHz, RTCCL = 00H (fmx	×/122)		22		μΑ
Interval timer operating current	_{IT} Notes 1, 2, 4	f _{MX} = 4 MHz, RTCCL = 00H (f _{MX}	= 4 MHz, RTCCL = 00H (f _{Mx} /122)				μΑ
Watchdog timer operating current	I _{WDT} Notes 1, 5, 6	fi∟ = 15 kHz	= 15 kHz				μΑ
LVD operating current	I _{LVD} Notes 1, 7				0.08		μΑ
Self-programming operating current	I _{FSP} Notes 1, 8				2.00	12.20	mA
BGO operating current	I _{BGO} Notes 1, 9				2.00	12.20	mA
SNOOZE operating	I _{SNOZ} Note 1	A/D converter operation	The mode is performed		0.50	1.10	mA
current		Notes 10,	During A/D conversion, AV _{DD} = V _{DD} = 3.0 V		1.20	2.04	
		Simplified SPI(CSI)/UART open	ration		0.70	1.54	
		DTC operation			3.10		

- Note 1. Current flowing to VDD
- Note 2. When the high-speed on-chip oscillator is stopped
- Note 3. Current flowing only to the real-time clock (RTC). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock is operating in operation mode or HALT mode.
- Note 4. Current flowing only to the interval timer. The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the interval timer is operating in operation mode or HALT mode. When the low-speed onchip oscillator is selected, also add IFIL.
- Note 5. When the high-speed on-chip oscillator and high-speed system clock are stopped.
- Note 6. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).

 The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is operating.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is operating.
- Note 8. Current flowing during self-programming
- Note 9. Current flowing during writing to the data flash
- Note 10. The current flowing into the AVDD is included.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fil: Low-speed on-chip oscillator clock frequency
- **Remark 3.** The temperature condition for the TYP. value is $TA = 25^{\circ}C$

• AFE functions

(Ta = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
24-bit $\Delta\Sigma$ A/D converter operating current	IDSAD	Normal mode Notes 1, 2 Circuits that operate: ABGR, REGA, SBIAS, VREFAMP, PGA, 24-bit $\Delta\Sigma$ A/D converter, and digital filter Differential input mode OSR = 256 SBIAS lout = 0 mA		0.94	1.46	mA
		Low power mode Notes 1, 2 Circuits that operate: ABGR, REGA, SBIAS, VREFAMP, PGA, 24-bit $\Delta\Sigma$ A/D converter, and digital filter Differential input mode OSR = 256 SBIAS lout = 0 mA		0.60	0.91	mA
10-bit A/D converter operating current	IADC	During conversion at the highest speed Notes 1, 2 AVDD = 5.0 V		1.30	1.70	mA
Configurable amplifier operating current	Іамр	Normal mode Notes 1, 2 Circuits that operate: ABGR and configurable amplifier IL = 0 mA Per channel		0.13	0.24	mA
		High-speed mode Notes 1, 2 Circuits that operate: ABGR and configurable amplifier IL = 0 mA Per channel		0.30	0.45	mA
12-bit D/A converter operating current	IDAC	When AV _{DD} and AVss are selected as the reference voltage Notes 1, 2 Circuits that operate: ABGR and internal reference voltage (VREFDA)		0.61	0.97	mA

Note 1. Current flowing to AVDD

Note 2. Current flowing only to the circuits that operate shown in the Conditions column.

3.4 AC Characteristics

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

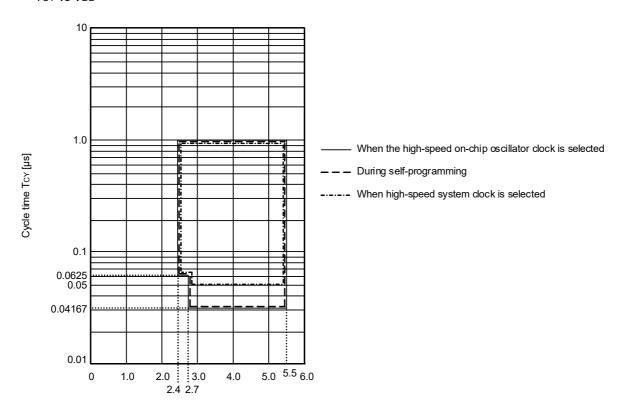
Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	Тсү	Main system clock (fmain) operation	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	0.04167		1	μs
			2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		In the self-programming mode	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	0.04167		1	μs
			2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
External system clock frequency	fEX	2.7 V ≤ VDD ≤ 5.5 V		1.0		20.0	MHz
		2.4 V ≤ V _{DD} < 2.7 V		1.0		8.0	MHz
External system clock input high-level width, low-level width	texh, texl	2.7 V ≤ VDD ≤ 5.5 V		24			ns
		2.4 V ≤ V _{DD} < 2.7 V		60			ns
TI00 to TI03, TI10, TI11 input high-level width, low-level width	tтін, tтіL			1/fмcк + 10			ns
Timer RJ input cycle	fc	TRJI00	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	100			ns
			2.4 V ≤ V _{DD} < 2.7 V	300			ns
Timer RJ input high-	tтлн,	TRJI00	$2.7~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	40			ns
level width, low-level width	t⊤JIL		2.4 V ≤ V _{DD} < 2.7 V	120			ns
Timer RG input high- level width, low-level width	tтgін, tтgіL	TRGIOA, TRGIOB		2.5/fcLK			ns
TO00 to TO03,	fто		$4.0 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$			12	MHz
TO10, TO11,			$2.7 \text{ V} \leq \text{VDD} \leq 4.0 \text{ V}$			6	MHz
TRJIO0, TRJO0, TRGIOA, TRGIOB output frequency			2.4 V ≤ V _{DD} < 2.7 V			3	MHz
PCLBUZ0 output	fPCL		4.0 V ≤ V _{DD} ≤ 5.5 V			12	MHz
frequency			2.7 V ≤ V _{DD} ≤ 4.0 V			6	MHz
			2.4 V ≤ V _{DD} < 2.7 V			3	MHz
Interrupt input high- level width, low-level width	tinth, tintl	INTP1 to INTP7	1	1			μs
RESET low-level width	trsL			10			μs

Remark fMCK: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))

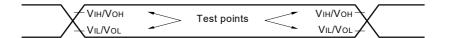
Minimum Instruction Execution Time During Main System Clock Operation

Tcy vs Vdd

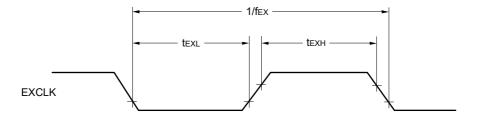


Supply voltage VDD [V]

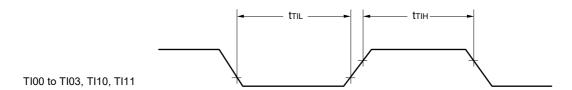
AC Timing Test Points

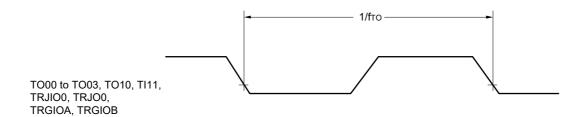


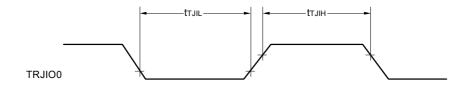
External System Clock Timing

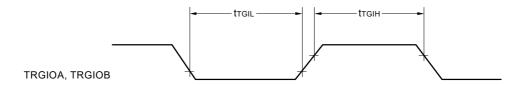


TI/TO Timing

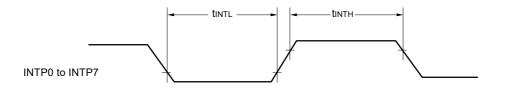




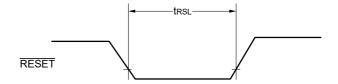




Interrupt Request Input Timing

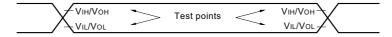


RESET Input Timing



3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

 $(TA = -40 \text{ to } +125^{\circ}C, 2.4 \text{ V} \le AVDD = VDD \le 5.5 \text{ V}, AVSS = VSS = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spee	Unit	
			MIN.	MAX.	
Transfer rate Note 1				fmck/12	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 2		2.0	Mbps

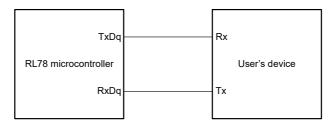
Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

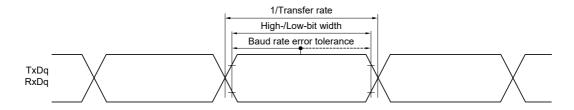
24 MHz (2.7 V \leq VDD \leq 5.5 V) 16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0, 1), g: PIM or POM number (g = 1)

Remark 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03))

(2) During communication at same potential (Simplified SPI(CSI) mode) (master mode, SCKp... internal clock output)

(Ta = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$	333		ns
			$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	666		ns
SCKp high-/low-level width	tkh1, tkl1	4.0 V ≤ V _{DD} ≤	5.5 V	tkcy1/2 - 24		ns
		2.7 V ≤ V _{DD} ≤	5.5 V	tkcy1/2 - 36		ns
		2.4 V ≤ V _{DD} ≤	5.5 V	tkcy1/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	tsiĸ1	4.0 V ≤ V _{DD} ≤	5.5 V	66		ns
		2.7 V ≤ V _{DD} ≤	5.5 V	66		ns
		$2.4~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$		113		ns
SIp hold time (from SCKp↑) Note 1	t KSI1			38		ns
Delay time from SCKp↓ to SOp output Note 2	tkso1	C = 30 pF Note	: 3		66.6	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKpţ" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. The SIp hold time becomes "from SCKpţ" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: Simplified SPI(CSI) number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM number (g = 1)
- Remark 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00, 01))

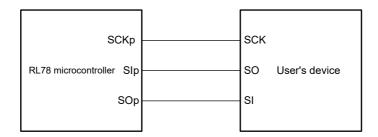
(3) During communication at same potential (Simplified SPI(CSI) mode) (slave mode, SCKp... external clock input)

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

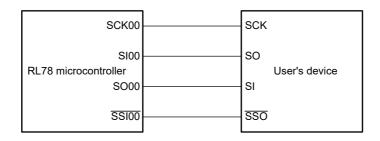
Parameter	Symbol	Conditions		HS (high-speed	d main) mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	$4.0 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$	20 MHz < fмск	16/ f мск		ns
			fмcк ≤ 20 MHz	12/ f мск		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	16 MHz < fмск	16/ f мск		ns
			fмск ≤ 16 MHz	12/ f мск		ns
		2.4 V ≤ V _{DD} ≤ 5.5 V		12/fмск and 1000		ns
SCKp high-/low-level width	tkH2, tkL2	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$		tkcy2/2 - 14		ns
		2.7 V ≤ V _{DD} ≤ 5.5 V		tkcy2/2 - 16		ns
		$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$		tkcy2/2 - 36		ns
SIp setup time (to SCKp↑) Note 2	tsik2	$2.7~V \leq V_{DD} \leq 5.5~V$		1/f _{MCK} + 40		ns
		2.4 V ≤ V _{DD} ≤ 5.5 V		1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 2	t _{KSI2}			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output	tkso2	C = 30 pF Note 4	$2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}$		2/fмск + 66	ns
Note 3			$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$		2/fмск + 113	ns
SSI00 setup time	tssıĸ	DAPmn = 0	$2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}$	240		ns
			$2.4~V \leq V_{DD} \leq 5.5~V$	400		ns
		DAPmn = 1	$2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}$	1/f _{MCK} + 240		ns
			$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	1/f _{MCK} + 400		ns
SSI00 hold time	tĸssı	DAPmn = 0	$2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}$	1/f _{MCK} + 240		ns
			$2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}$	1/f _{MCK} + 400		ns
		DAPmn = 1	$2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}$	240		ns
			$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	400		ns

- **Note 1.** The maximum transfer rate in the SNOOZE mode is 1 Mbps.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SOp output lines.
- Caution Select the normal input buffer for the SIp and SCKp pins and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: Simplified SPI(CSI) number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM number (g = 1)
- Remark 2. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, $% \left(\frac{1}{2}\right) =\frac{1}{2}\left(\frac{1}{2}\right) =$
 - n: Channel number (mn = 00, 01))

Simplified SPI(CSI) mode connection diagram (during communication at same potential)



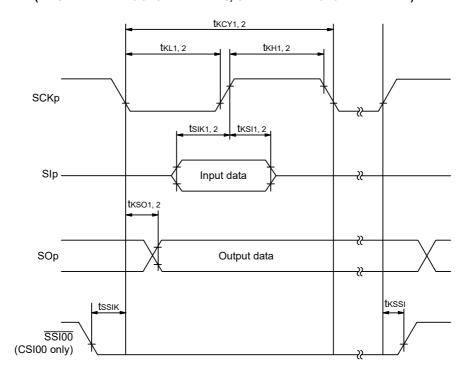
Simplified SPI(CSI) mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))



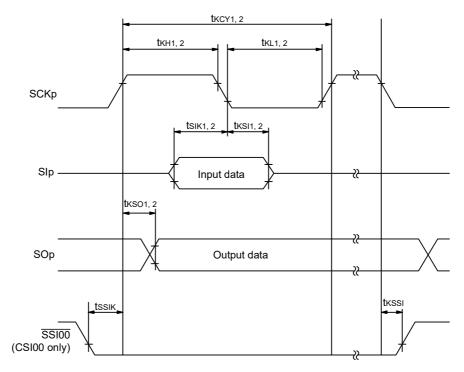
Remark 1. p: Simplified SPI(CSI) number (p = 00, 01)

Remark 2. m: Unit number, n: Channel number (mn = 00, 01)

Simplified SPI(CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI(CSI) mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: Simplified SPI(CSI) number (p = 00, 01)

Remark 2. m: Unit number, n: Channel number (mn = 00, 01)

(4) During communication at same potential (simplified I²C mode)

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-spee	d main) mode	Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega$		400 Note 1	kHz
		$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF, } R_b = 3 \text{ k}\Omega$		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1200		ns
		$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF, } R_b = 3 \text{ k}\Omega$	4600		ns
Hold time when SCLr = "H"	tнісн	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega$	1200		ns
		$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF, } R_b = 3 \text{ k}\Omega$	4600		ns
Data setup time (reception)	tsu: dat	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega$	1/fмск + 220 Note 2		ns
		$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF, } R_b = 3 \text{ k}\Omega$	1/f _{MCK} + 580 Note 2		ns
Data hold time (transmission)	thd: dat	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega$	0	770	ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 3 \text{ k}\Omega$	0	1420	ns

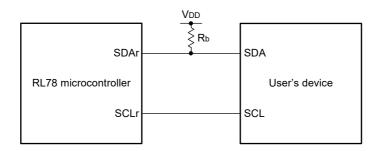
Note 1. The value must also be equal to or less than fmck/4.

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

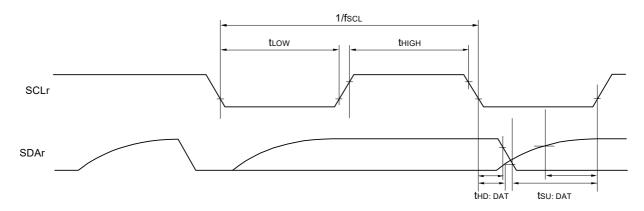
(Remarks are listed on the next page.)

Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



 $\textbf{Remark 1.} \ \ \mathsf{Rb} \ [\Omega] : \textbf{Communication line (SDAr) pull-up resistance, Cb} \ [F] : \textbf{Communication line (SDAr, SCLr) load capacitance}$

Remark 2. r: IIC number (r = 00, 01), g: PIM number (g = 1), h: POM number (h = 1)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0),

n: Channel number (n = 0, 1), mn = 00, 01)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(1/2)

Parameter	Symbol		Conditions		HS (high-speed main) mode	
				MIN.	MAX.	
Transfer rate		Reception	$4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V}, 2.7 \text{ V} \le V_b \le 4.0 \text{ V}$		f _{MCK} /12 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} \frac{Note 2}{}$		2.0	Mbps
		-	$2.7 \text{ V} \le V_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le V_{b} \le 2.7 \text{ V}$		f _{MCK} /12 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK} \frac{Note}{2}$		2.0	Mbps
		-	$2.4 \; \text{V} \leq \text{V}_{\text{DD}} < 3.3 \; \text{V}, 1.6 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \; \text{V}$		f _{MCK} /12 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 2		2.0	Mbps

- Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.
- Note 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

24 MHz (2.7 V \leq VDD \leq 5.5 V) 16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- Remark 1. Vb [V]: Communication line voltage
- Remark 2. q: UART number (q = 0, 1), g: PIM or POM number (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00, 01)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

(2/2)

Parameter	Symbol		Conditions		HS (high-speed main) mode	
				MIN.	MAX.	
Transfer rate		Transmission	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$		Note 1	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$		2.0 Note 2	Mbps
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		Note 3	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$		1.2 Note 4	Mbps
			$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$		Note 5	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$		0.43 Note 6	Mbps

Note 1. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq VDD \leq 5.5 V and 2.7 V \leq Vb \leq 4.0 V

Note 2. This value as an example is calculated when the conditions described in the "Conditions" column are met.

Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq VDD < 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met.

Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



^{*} This value is the theoretical value of the relative difference between the transmission and reception sides.

^{*} This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 5. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate

Expression for calculating the transfer rate when 2.4 V \leq VDD < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \text{In} (1 - \frac{1.5}{\text{Vb}})\} }{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

- Note 6. This value as an example is calculated when the conditions described in the "Conditions" column are met.

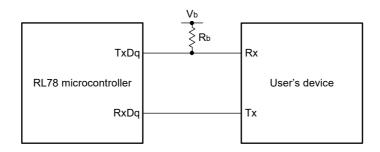
 Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

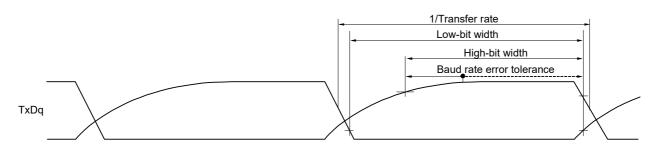


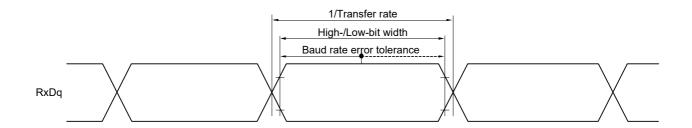
^{*} This value is the theoretical value of the relative difference between the transmission and reception sides.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remark 1.** Rb [Ω]: Communication line (TxDq) pull-up resistance,
 - Cb [F]: Communication line (TxDq) load capacitance, Vb [V]: Communication line voltage
- Remark 2. q: UART number (q = 0, 1), g: PIM or POM number (g = 1)
- Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00, 01))

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI(CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(1/3)

Parameter	Symbol		Conditions	HS (high-speed	l main) mode	Unit
				MIN.	MAX.	
SCKp cycle time	t ксу1	tkcy1 ≥ 4/fclk	$ 4.0 \ V \leq V_{DD} \leq 5.5 \ V, $ $ 2.7 \ V \leq V_b \leq 4.0 \ V, $ $ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega $	600		ns
			$2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V},$ $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1000		ns
			$2.4 \ V \leq V_{DD} < 3.3 \ V,$ $1.6 \ V \leq V_b \leq 2.0 \ V,$ $C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$	2300		ns
SCKp high-level width	t _{KH1}	$ 4.0 \ V \le V_{DD} \le 5.5 \ V, $ $ 2.7 \ V \le V_b \le 4.0 \ V, $ $ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega $		tксу1/2 - 150		ns
		$\begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$		tксү1/2 - 340		ns
		$2.4 \text{ V} \leq \text{V}_{DD} < \\ 1.6 \text{ V} \leq \text{V}_{b} \leq 2 \\ C_{b} = 30 \text{ pF, Re}$.0 V,	tксү1/2 - 916		ns
SCKp low-level width	w-level width $t_{KL1} \qquad \qquad 4.0 \text{ V} \leq \text{V}_{DD} \leq 2.7 \text{ V} \leq \text{V}_b \leq \\ C_b = 30 \text{ pF, F}$.0 V,	tксү1/2 - 24		ns
		$2.7 \text{ V} \leq \text{V}_{DD} < \\ 2.3 \text{ V} \leq \text{V}_{b} \leq 2 \\ \text{C}_{b} = 30 \text{ pF, Rt}$.7 V,	tксү1/2 - 36		ns
		$2.4 \text{ V} \leq \text{V}_{DD} < \\ 1.6 \text{ V} \leq \text{V}_{b} \leq 2 \\ C_{b} = 30 \text{ pF, Re}$.0 V,	tксү1/2 - 100		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI(CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(2/3)

Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↑) ^{Note}	tsıĸı	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$	162		ns
		$\label{eq:controller} \begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 2.7 \ k\Omega \end{split}$	354		ns
		$2.4 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V}, \\ C_{b} = 30 \text{ pF}, R_{b} = 5.5 \text{ k}\Omega$	958		ns
SIp hold time (from SCKp↑) ^{Note}	tksii	$\begin{aligned} 4.0 & \ V \leq V_{DD} \leq 5.5 \ V, \\ 2.7 & \ V \leq V_b \leq 4.0 \ V, \\ C_b & = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned}$	38		ns
		$\label{eq:controller} \begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 2.7 \ k\Omega \end{split}$	38		ns
		$\label{eq:controller} \begin{split} 2.4 \ V &\leq V_{DD} < 3.3 \ V, \\ 1.6 \ V &\leq V_{b} \leq 2.0 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 5.5 \ k \Omega \end{split}$	38		ns
Delay time from SCKp↓ to SOp output ^{Note}	tkso1	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V}, \\ C_{b} = 30 \text{ pF}, \text{ R}_{b} = 1.4 \text{ k}\Omega \end{aligned}$		200	ns
		$\label{eq:section} \begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 2.7 \ k\Omega \end{split}$		390	ns
		$\label{eq:controller} \begin{split} 2.4 & \ V \leq V_{DD} < 3.3 \ V, \\ 1.6 & \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI(CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(3/3)

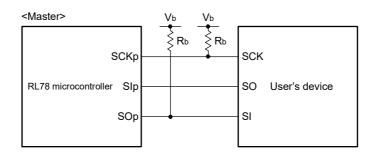
Parameter	Symbol	Conditions	HS (high-spee	ed main) mode	Unit
			MIN.	MAX.	
SIp setup time (to SCKp↓) ^{Note}	tsıĸı	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$	88		ns
		$\begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 2.7 \ k \Omega \end{split}$	88		ns
		$\label{eq:controller} \begin{split} 2.4 \ V &\leq V_{DD} < 3.3 \ V, \\ 1.6 \ V &\leq V_{b} \leq 2.0 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 5.5 \ k \Omega \end{split}$	220		ns
SIp hold time (from SCKp↓) ^{Note}	tksii	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$	38		ns
		$\label{eq:controller} \begin{split} 2.7 \ V &\leq V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 2.7 \ k\Omega \end{split}$	38		ns
		$\label{eq:controller} \begin{split} 2.4 \ V &\leq V_{DD} < 3.3 \ V, \\ 1.6 \ V &\leq V_{b} \leq 2.0 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 5.5 \ k \Omega \end{split}$	38		ns
Delay time from SCKp↑ to SOp output ^{Note}	tkso1	$\begin{aligned} 4.0 & \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ 2.7 & \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$		50	ns
		$\begin{split} 2.7 & \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 30 \text{ pF}, \text{ R}_{b} = 2.7 \text{ k}\Omega \end{split}$		50	ns
		$\begin{aligned} 2.4 & \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}, \\ 1.6 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned}$		50	ns

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

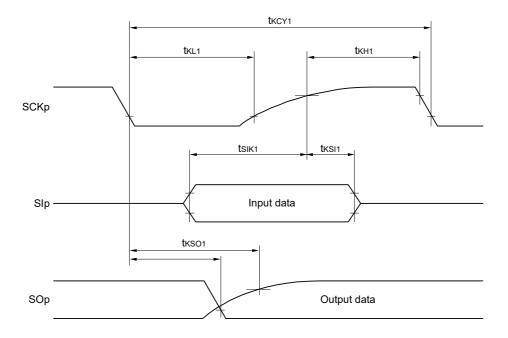
(Remarks are listed on the next page.)

Simplified SPI (CSI) mode connection diagram (during communication at different potential

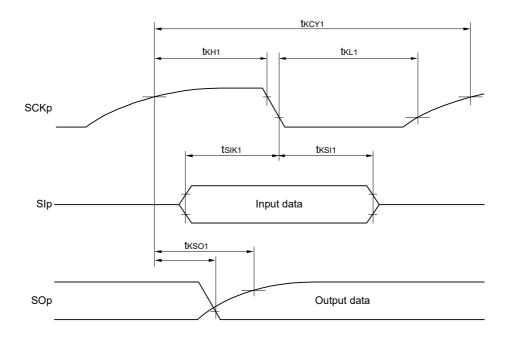


- Remark 1. Rb [Ω]: Communication line (SCKp, SOp) pull-up resistance, Cb [F]: Communication line (SCKp, SOp) load capacitance, Vb [V]: Communication line voltage
- Remark 2. p: Simplified SPI(CSI) number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00, 01))

Simplified SPI(CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI(CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: Simplified SPI(CSI) number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI(CSI) mode) (slave mode, SCKp... external clock input)

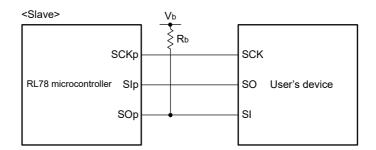
(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol	Co	nditions	HS (high-spee	ed main) mode	Unit	
				MIN.	MAX.		
SCKp cycle time Note 1	tkcy2	$4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V},$	20 MHz < fмск ≤ 24 MHz	24/ f мск		ns	
		$2.7~V \leq V_b \leq 4.0~V$	8 MHz < fмск ≤ 20 MHz	20/fмск		ns	
		4 MHz < fмcк ≤ 8 MHz	16/ f мск		ns		
			fмcк ≤ 4 MHz	12/ f мск		ns	
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$	20 MHz < fмск ≤ 24 MHz	32/ f мск		ns	
		16 MHz < fмск ≤ 20 MHz	28/ f мск		ns		
		8 MHz < fмcк ≤ 16 MHz	24/ f мск		ns		
			4 MHz < fмcк ≤ 8 MHz	16/ f мск		ns	
		fмcк ≤ 4 MHz	12/ f мск		ns		
		$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$	20 MHz < fмск ≤ 24 MHz	72/ f мск		ns	
		$1.6~V \leq V_b \leq 2.0~V$	16 MHz < fмск ≤ 20 MHz	64/ f мск		ns	
			8 MHz < fмcк ≤ 16 MHz	52/ f мск		ns	
			4 MHz < fмcк ≤ 8 MHz	32/ f мск		ns	
				fмcк ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level	tkH2, tkL2	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, 2$	2.7 V ≤ V _b ≤ 4.0 V	tkcy2/2 - 24		ns	
width		$2.7 \text{ V} \le V_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \le V_{b} \le 2.7 \text{ V}$		tkcy2/2 - 36		ns	
		$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V}, 1$	$1.6~V \le V_b \le 2.0~V$	tkcy2/2 - 100		ns	
SIp setup time	tsık2	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, 2$	2.7 V ≤ V _b ≤ 4.0 V	1/fмск + 40		ns	
(to SCKp↑) Note 2		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V}, 2$	$2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$	1/fмск + 40		ns	
		$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V}, 1$	$1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$	1/fмск + 60		ns	
SIp hold time (from SCKp↑) Note 2	tksi2			1/fмск + 62		ns	
Delay time from	tkso2	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, 2$	2.7 V ≤ V _b ≤ 4.0 V,		2/f _{MCK} + 240	ns	
SCKp↓ to SOp output Note 3		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$					
		-	$2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_{b} \leq 2.7 \ V,$		2/fмск + 428	ns	
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ l}$					
		$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V}, 1$ $C_b = 30 \text{ pF}, R_b = 5.5 \text{ N}$			2/fмск + 1146	ns	

(Notes, Cautions, and Remarks are listed on the next page.)

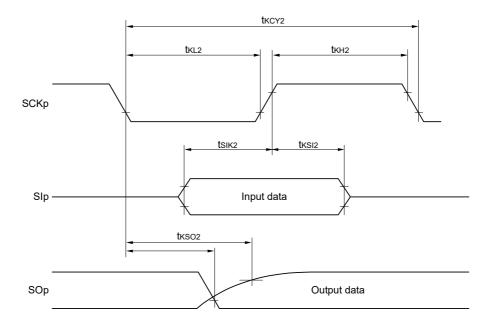
- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp and SCKp pins, and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Simplified SPI(CSI) mode connection diagram (during communication at different potential)

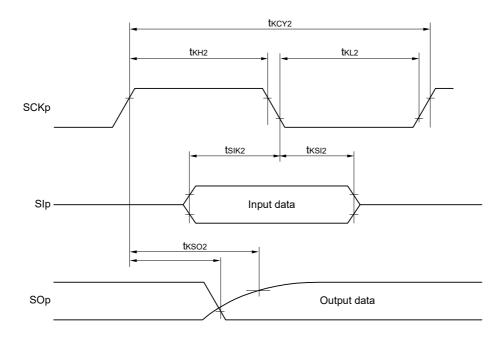


- **Remark 1.** Rb [Ω]: Communication line (SOp) pull-up resistance, Cb [F]: Communication line (SOp) load capacitance, Vb [V]: Communication line voltage
- Remark 2. p: Simplified SPI(CSI) number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00, 01))
- Remark 4. Communication at different potential cannot be performed during clocked serial communication with the slave select function.

Simplified SPI(CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI(CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: Simplified SPI(CSI) number (p = 00, 01), m: Unit number (m = 0), n: Channel number (n = 0, 1), g: PIM or POM number (g = 1)

Remark 2. Communication at different potential cannot be performed during clocked serial communication with the slave select function.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(1/2)

(1A = -40 to +125°C, 2.4 V ≤ AVI	İ	· ·		1	(1/2
Parameter	Symbol	Conditions	HS (high-spe	eed main) mode	Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V},$		400 Note 1	kHz
		$2.7~V \leq V_b \leq 4.0~V,$			
		C_b = 50 pF, R_b = 2.7 k Ω			
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$		400 Note 1	kHz
		$2.3 \text{ V} \le V_b \le 2.7 \text{ V},$			
		C_b = 50 pF, R_b = 2.7 k Ω			
		$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$		100 Note 1	kHz
		$2.7 \text{ V} \le V_b \le 4.0 \text{ V},$			
		$C_b = 100 \text{ pF}, R_b = 2.8 \text{ k}\Omega$			
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$		100 Note 1	kHz
		$2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$			
		$C_b = 100 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		2.4 V ≤ V _{DD} < 3.3 V,		100 Note 1	kHz
		$1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}.$		100	11112
		$C_b = 100 \text{ pF}, R_b = 5.5 \text{ k}\Omega$			
Hold time when SCLr = "L"	tLOW	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$	1200		ns
Hold time when SCLI – L	tLOW	$2.7 \text{ V} \le \text{Vb} \le 3.3 \text{ V},$ $2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V},$	1200		113
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$	1200		
		$2.7 \text{ V} \le \text{VDD} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$	1200		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
			4000		
		$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$	4600		ns
		$2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 2.8 \text{ k}\Omega$			
			1000		
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$	4600		ns
		$2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$			
		$C_b = 100 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V},$	4600		ns
		$1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V},$			
		$C_b = 100 \text{ pF}, R_b = 5.5 \text{ k}\Omega$			
Hold time when SCLr = "H"	t HIGH	$4.0 \text{ V} \leq V_{DD} \leq 5.5 \text{ V},$	620		ns
		$2.7 \text{ V} \le V_b \le 4.0 \text{ V},$			
		$C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega$			
		$2.7 \text{ V} \le V_{DD} \le 4.0 \text{ V},$	500		ns
		$2.3~V \leq V_b \leq 2.7~V,$			
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$	2700		ns
		$2.7~V \leq V_b \leq 4.0~V,$			
		C_b = 100 pF, R_b = 2.8 k Ω			
		$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$	2400		ns
		$2.3 \text{ V} \le V_b \le 2.7 \text{ V},$			
		$C_b = 100 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$	1830		ns
		$1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V},$			
		$C_b = 100 \text{ pF}, R_b = 5.5 \text{ k}\Omega$			

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(TA = -40 to +125°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

(2/2)

Parameter	Symbol	Conditions	HS (high-speed m	nain) mode	Unit
			MIN.	MAX.	
Data setup time (reception)	tsu:dat	$ \begin{aligned} 4.0 & \ V \le V_{DD} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	1/f _{MCK} + 340 Note 1		ns
		$\label{eq:controller} \begin{split} 2.7 \ V & \leq V_{DD} < 4.0 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1/f _{MCK} + 340 Note 2		ns
		$ \begin{aligned} &4.0 \; \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \; \text{V}, \\ &2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ &C_{\text{b}} = 100 \; \text{pF}, \; R_{\text{b}} = 2.8 \; \text{k}\Omega \end{aligned} $	1/f _{MCK} + 760 Note 2		ns
		$ \begin{aligned} &2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ &2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ &C_{b} = 100 \text{ pF}, \text{ R}_{b} = 2.7 \text{ k}\Omega \end{aligned} $	1/fмcк + 760 Note 2		ns
		$ \begin{aligned} &2.4 \text{ V} \leq \text{V}_{DD} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V}, \\ &C_{b} = 100 \text{ pF}, \text{ R}_{b} = 5.5 \text{ k}\Omega \end{aligned} $	1/f _{MCK} + 570 Note 2		ns
Data hold time (transmission)	thd:dat	$ \begin{aligned} 4.0 & \ V \le V_{DD} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	0	770	ns
		$2.7 \ V \leq V_{DD} < 4.0 \ V,$ $2.3 \ V \leq V_b \leq 2.7 \ V,$ $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega$	0	770	ns
		$ \begin{aligned} &4.0 \; \text{V} \leq \text{V}_{\text{DD}} \leq 5.5 \; \text{V}, \\ &2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ &C_{\text{b}} = 100 \; \text{pF}, \; R_{\text{b}} = 2.8 \; \text{k}\Omega \end{aligned} $	0	1420	ns
		$ \begin{aligned} 2.7 & \ V \le V_{DD} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	0	1420	ns
		$\label{eq:second-state} \begin{split} 2.4 & \ V \leq V_{DD} < 3.3 \ V, \\ 1.6 & \ V \leq V_{b} \leq 2.0 \ V, \\ C_{b} = 100 \ pF, \ R_{b} = 5.5 \ k\Omega \end{split}$	0	1215	ns

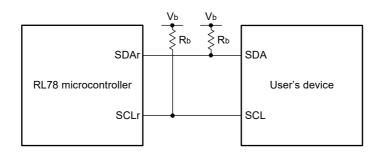
Note 1. The value must also be equal to or less than fmck/4.

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance) mode for the SDAr pin and the N-ch open drain output (VDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

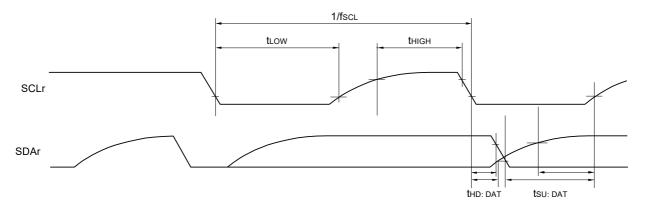
(Remarks are listed on the next page.)

Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- Remark 1. Rb $[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, Cb [F]: Communication line (SDAr, SCLr) load capacitance, Vb [V]: Communication line voltage
- Remark 2. r: IIC number (r = 00, 01), g: PIM, POM number (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0),

 n: Channel number (n = 0), mn = 00, 01)

3.6 Analog Characteristics

3.6.1 Programmable gain instrumentation amplifier and 24-bit $\Delta\Sigma$ A/D converter

(1) Analog input in differential input mode

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dofr = 0 mV, Vcom = 1.0 V, external clock input used)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Full-scale differential input voltage range	VID	VID = (PGAxP - PGAxN) (x = 0 to 3)		± 800 /Gtotal		mV
Input voltage range	Vı	Each of PGAxP and PGAxN pins (x = 0 to 3)	0.2		1.8	V
Common mode input voltage	Vсом	dofr = 0 mV	0.2+(VID X GSET1)/2		1.8-(VID X GSET1)/2	V
Input bias current	lin	Vi = 1.0 V			± 50	nA
Input offset current	INOFR	Vi = 1.0 V			± 20	nA

(2) Analog input in single-ended input mode

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dofr = 0 mV, Vcom = 1.0 V, external clock input used)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage range	Vı	Each of PGAxP and PGAxN pins	0.2		1.8	V
		(x = 0 to 3)				
		GSET1 = 1, GSET2 = 1				
Input bias current	lin	VI = 1.0 V			± 50	nA

(3) Programmable gain instrumentation amplifier and 24-bit $\Delta\Sigma$ A/D converter

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dofr = 0 mV, Vcom = 1.0 V, external clock input used, in differential input mode) (1/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES				24	bit
Sampling frequency	fs1	Normal mode		1		MHz
	fs2	Low power mode		0.125		MHz
Output data rate	fDATA1	Normal mode	0.48828		15.625	ksps
	fDATA2	Low power mode	61.03615		1953.125	sps
Gain setting range	GTOTAL	GTOTAL = GSET1 × GSET2	1		64	V/V
1st gain setting range	GSET1	In differential input mode only		1, 2, 3, 4, 8		V/V
2nd gain setting range	GSET2	In differential input mode only		1, 2, 4, 8		V/V
Offset adjustment bit range	dоғғв			5		bit
Offset adjustment range	dofr	Referred to input	-164/GSET1		+164/GSET1	mV
Offset adjustment steps	dofs	Referred to input		11/GSET1		mV

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V, normal mode: fs1 = 1 MHz, FDATA1 = 3.90625 ksps, low-power mode: fs2 = 0.125 MHz, FDATA2 = 488.28125 sps, SBIAS = 1.2 V, dofr = 0 mV, Vcom = 1.0 V, external clock input used, in differential input mode) (2/2)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Gain error	EG	TA = 25°C GSET1 = 1, GSET2 = 1 Excluding SBIAS error		±0.2	±2.7	%
		TA = 25°C GSET1 = 8, GSET2 = 4 Excluding SBIAS error		±0.1		%
Gain drift ^{Note}	dEG	GSET1 = 1, GSET2 = 1 Excluding SBIAS drift		(5.6)	(22.0)	ppm/°C
		GSET1 = 8, GSET2 = 4 Excluding SBIAS drift		(9.1)		ppm/°C
Offset error	Eos	TA = 25°C GSET1 = 1, GSET2 = 1 Referred to input		±0.32	±2.90	mV
		TA = 25°C GSET1 = 8, GSET2 = 4 Referred to input		±0.03		mV
Offset drift Note	dEos	GSET1 = 1, GSET2 = 1 Referred to input		(±0.02)	(±6.00)	μV/°C
		GSET1 = 8, GSET2 = 4 Referred to input		(±0.02)		μV/°C
SND ratio	SNDR	GSET1 = 1, GSET2 = 1, fin = 50 Hz Normal mode, pin = -1 dBFS	(82)	(85)		dB
		GSET1 = 8, GSET2 = 4, fin = 50 Hz Normal mode, pin = -1 dBFS	(73)	(80)		dB
Noise	Vn	GSET1 = 1, GSET2 = 1, OSR = 2048		(13)		μVRms
		GSET1 = 8, GSET2 = 4, OSR = 2048		(0.6)		μVRms
Integral non-linearity error	INL	GSET1 = 1, GSET2 = 1, OSR = 2048		(±10)		ppmFS
Common mode rejection ratio	CMRR	VCOM = 1.0 ± 0.8 V, fin = 50 Hz GSET1 = 1, GSET2 = 1 Differential input mode	(72)	(90)		dB
Power supply rejection ratio	PSRR	AVDD = 2.7 to 5.5 V GSET1 = 1, GSET2 = 1 Differential input mode		(85)		dB
$\Delta\Sigma$ A/D converter input clock frequency	fadc		3.8	4	4.2	MHz

Note Calculate the gain drift and offset drift by using the following expression (for 125°C products):

For gain drift: $(MAX(Eg(T_{(-40)} to T_{(125)})) - MIN(Eg(T_{(-40)} to T_{(125)}))) / (125°C - (-40°C))$

For offset drift: (MAX(Eos(T(-40) to T(125))) - MIN(Eos(T(-40) to T(125)))) / (125°C - (-40°C))

MAX(Eg(T(-40) to T(125))): The maximum value of gain error when the temperature range is -40°C to 125°C MIN(Eg(T(-40) to T(125))): The minimum value of gain error when the temperature range is -40°C to 125°C MAX(Eos(T(-40) to T(125))): The maximum value of offset error when the temperature range is -40°C to 125°C MIN(Eos(T(-40) to T(125))): The minimum value of offset error when the temperature range is -40°C to 125°C

Remark In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.



3.6.2 Sensor power supply (SBIAS)

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V, COUT = 0.22 μ F, VOUT = 1.0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Output voltage range	Vouт		0.5		2.2	V
Output voltage setting steps	VSTEP			0.1		V
Output voltage precision	VA	IOUT = 1 mA	(-3)		(+3)	%
Maximum output current	Іоит		5			mA
Short circuit current	ISHORT	Vout = 0 V		40	65	mA
Load regulation	LR	1 mA ≤ Iout ≤ 5 mA			(15)	mV
Power supply rejection ratio	PSRR	AVDD = 5.0 V + 0.1 Vpp ripple f = 100 Hz, Iout = 2.5 mA	(45)	(50)		dB

Remark In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

3.6.3 Temperature sensor

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature coefficient for sensor	TCsns			(756)		μV/°C
Sensor output voltage	VTEMP	TA = 25°C		226.4		mV

Remark In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

3.6.4 A/D converter characteristics

(1) When positive reference voltage (+) = AVDD (ADREFP1 = 0, ADREFP0 = 0), negative reference voltage (-) = AVSS (ADREFM = 0), pins subject to A/D conversion: ANI0 to ANI9 and SBIAS

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = AVDD, negative reference voltage (-) = AVss)

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$4.0 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$		1.2	±6.5	LSB
		ANI0 to ANI9, SBIAS	$2.7 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	4.0 V ≤ AV _{DD} ≤ 5.5 V	2.125		39	μs
			$2.7 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$	3.1875		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	4.0 V ≤ AV _{DD} ≤ 5.5 V			±0.50	%FSR
		ANI0 to ANI9, SBIAS	$2.7 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$			±0.60	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	4.0 V ≤ AV _{DD} ≤ 5.5 V			±0.50	%FSR
		ANI0 to ANI9, SBIAS	$2.7 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	4.0 V ≤ AV _{DD} ≤ 5.5 V			±3.5	LSB
		ANI0 to ANI9, SBIAS	$2.7 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.7 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$			±2.0	LSB
Analog input voltage	Vain	ANI0 to ANI9	•	AVss		AV _{DD}	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Caution The number of pins depends on the product. For details, see a list of pin functions.

(2) When positive reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), negative reference voltage (-) = AVss (ADREFM = 0), pins subject to A/D conversion: ANI0 to ANI9 and SBIAS

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = VBGR, negative reference voltage (-) = AVss)

Parameter	Symbol	Condi	tions	MIN.	TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	$2.7 \text{ V} \leq \text{AV}_{DD} \leq 5.5 \text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	$2.7 \text{ V} \le \text{AV}_{DD} \le 5.5 \text{ V}$			±0.60	%FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.7 \text{ V} \le \text{AV}_{DD} \le 5.5 \text{ V}$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	2.7 V ≤ AV _{DD} ≤ 5.5 V			±1.0	LSB
Internal reference voltage (+)	V _{BGR}	$2.7 \text{ V} \le \text{AV}_{\text{DD}} \le 5.5 \text{ V}$		V _{BGR} Note 3		V	
Analog input voltage	Vain	ANI0 to ANI9		0		V _{BGR}	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. See the Internal reference voltage characteristics.

3.6.5 12-bit D/A converter

(1) When positive reference voltage (+) = AVDD (DACVRF = 0)

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = AVDD)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	DARES				(12)	bit
Output voltage range	DAOUT	12-bit resolution	0.35		AVDD-0.47	V
Integral non-linearity error	DAILE	12-bit resolution			±4.0	LSB
Differential non-linearity error	DADLE	12-bit resolution			±1.0	LSB
Offset error	DAErr	12-bit resolution			±30	mV
Gain error	DAEG	12-bit resolution			±20	mV
Settling time	DAtset	12-bit resolution, CL = 50 pF, RL = 10 k Ω			(60)	μs

Remark 1. In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

Remark 2. The 12-bit D/A converter characteristics are the values obtained with the configurable amplifier connected.

(2) When positive reference voltage (+) = internal reference voltage (DACVRF = 1)

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, positive reference voltage (+) = VREFDA)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	DARES				(8)	bit
Internal reference voltage	VREFDA	8-bit resolution	1.34	1.45	1.54	V
Output voltage range	DAOUT	8-bit resolution	0.35		VREFDA	V
Integral non-linearity error	DAILE	8-bit resolution			±1.0	LSB
Differential non-linearity	DADLE	8-bit resolution			±1.0	LSB
error						
Offset error	DAErr	8-bit resolution			±30	mV
Gain error	DAEG	8-bit resolution			±20	mV
Settling time	DAtset	8-bit resolution, CL = 50 pF, RL = 10 k Ω			(60)	μs

Remark 1. In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.

Remark 2. The 12-bit D/A converter characteristics are the values obtained with the configurable amplifier connected.

Remark 3. Offset error and gain error do not include error in the internal reference voltage.

3.6.6 Configurable amplifier

(TA = -40 to +125°C, 2.7 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V, Vcom = 1/2 AVDD, internally connected voltage follower)

AMP0 configuration SW setting: Positive (+) pin = ANX1, negative (-) pin = ANX0 AMP1 configuration SW setting: Positive (+) pin = ANX3, negative (-) pin = ANX2 AMP2 configuration SW setting: Positive (+) pin = ANX5, negative (-) pin = ANX4

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage	Vin		AVss		AVDD	V
Output voltage	Vol	IL= -1 mA, AV _{DD} = 2.7 to 5.5 V		AVss +0.02	AVss +0.07	V
	Vон	IL= 1 mA, AV _{DD} = 2.7 to 5.5 V	AV _{DD} -0.15	AV _{DD} -0.02		V
Maximum output current	Іоит	4.5 V ≤ AVDD ≤ 5.5 V	±10			mA
		2.7 V ≤ AVDD ≤ 5.5 V	±5			mA
Input-referred offset voltage	Voff	TA = 25°C without trimming IL = 0 mA, VCOM = 1.0 V		±1	±4	mV
		TA = 25°C with trimming IL = 0 mA, VCOM = 1.0 V			±0.35	mV
Temperature coefficient for inputreferred offset voltage	Vотс	IL = 0 mA		(±2)	(±8)	μV/°C
Slew rate	SR1	Normal mode $C_L = 50 \text{ pF, } R_L = 10 \text{ k}\Omega$		(0.1)		V/µs
	SR2	High-speed mode $C_L = 50$ pF, $R_L = 10$ kΩ		(0.8)		V/µs
Gain bandwidth	GBW1	Normal mode $C_L = 50 \text{ pF, } R_L = 10 \text{ k}\Omega$		(350)		kHz
	GBW2	High-speed mode $C_L = 50$ pF, $R_L = 10$ kΩ		(1.8)		MHz
Phase margin	θМ1	Normal mode $C_L = 50 \text{ pF, } R_L = 10 \text{ k}\Omega$		(70)		deg
	θМ2	High-speed mode $C_L = 50$ pF, $R_L = 10$ kΩ		(60)		deg
Settling time	tset1	Normal mode $CL = 50 \text{ pF}, RL = 10 \text{ k}\Omega$		(20)		μs
	tset2	High-speed mode $CL = 50$ pF, $RL = 10$ kΩ		(10)		μs
Peak-to-peak voltage noise	Enb	0.1 to 10 Hz Normal mode CL = 50 pF, RL = 10 kΩ		(2.0)		μVrms
Input-referred noise	En	f = 1 kHz Normal mode CL = 50 pF, RL = 10 kΩ		(70)		nV/√Hz
Common mode rejection ratio	CMRR	$f = 1 \text{ KHz}$, $CL = 50 \text{ pF}$, $RL = 10 \text{ k}\Omega$		(70)		dB
Power supply rejection ratio	PSRR	$2.7 \text{ V} \le \text{AV}_{DD} \le 5.5 \text{ V}$ CL = 50 pF, RL = 10 k Ω		(62)		dB

(Remarks are listed on the next page.)



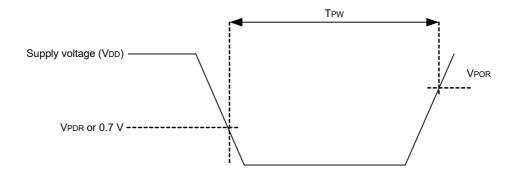
- Remark 1. In the ratings column, values in parentheses are the target design values and therefore are not tested for shipment.
- **Remark 2.** The TYP. conditions are the conditions when $T_A = 25^{\circ}C$ and AVDD = 5.0 V.
- Remark 3. Unless otherwise specified, offset trimming has proceeded.
- Remark 4. Unless otherwise specified, values are for operation in normal mode.

3.6.7 POR characteristics

(TA = -40 to +125°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power on/down reset threshold	VPOR	Voltage threshold on VDD rising	1.48	1.56	1.62	V
	VPDR	Voltage threshold on VDD falling Note 1	1.47	1.55	1.61	V
Minimum pulse width Note 2	Tpw		300			μs

- **Note 1.** However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 3.4 AC Characteristics.
- Note 2. Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.8 LVD characteristics

(1) LVD detection voltage in reset mode and interrupt mode

(Ta = -40 to +125°C, VPDR \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Voltage detection	Supply voltage level	VLVD0	Rising edge	4.62	4.74	4.94	V
threshold			Falling edge	4.52	4.64	4.84	V
		VLVD1	Rising edge	4.50	4.62	4.82	V
			Falling edge	4.40	4.52	4.71	V
		VLVD2	Rising edge	4.30	4.42	4.61	V
			Falling edge	4.21	4.32	4.51	V
		VLVD3	Rising edge	3.13	3.22	3.39	V
			Falling edge	3.07	3.15	3.31	V
		VLVD4	Rising edge	2.95	3.02	3.17	V
			Falling edge	2.89	2.96	3.09	V
		VLVD5	Rising edge	2.74	2.81	2.95	V
			Falling edge	2.68	2.75	2.88	V
		VLVD6	Rising edge	2.55	2.61	2.74	V
			Falling edge	2.49	2.55	2.67	V
Minimum pulse wid	dth	tLW		300			μs
Detection delay time						300	μs

(2) LVD detection voltage in interrupt & reset mode

(TA = -40 to +125°C, VPDR \leq AVDD = VDD \leq 5.5 V, AVSS = VSS = 0 V)

Parameter	Symbol		Condi	tions	MIN.	TYP.	MAX.	Unit
Voltage detection	VLVDD6	VPOC2,	VPOC1, VPOC0 = 0, 0, 0, fall	ling reset voltage	2.49	2.55	2.67	V
threshold	VLVDD4		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.95	3.02	3.17	V
				Falling interrupt voltage	2.89	2.96	3.09	V
	VLVDD3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.13	3.22	3.39	V
				Falling interrupt voltage	3.07	3.15	3.31	V
	VLVDD5	VPOC2,	VPOC1, VPOC0 = 0, 0, 1, fall	ling reset voltage	2.68	2.75	2.88	V
	VLVDD2		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	4.30	4.42	4.61	V
				Falling interrupt voltage	4.21	4.32	4.51	V
	VLVDD5	VPOC2,	VPOC1, VPOC0 = 0, 1, 0, fall	ling reset voltage	2.68	2.75	2.88	V
	VLVDD1		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	4.50	4.62	4.82	V
				Falling interrupt voltage	4.40	4.52	4.71	V
	VLVDD5	VPOC2,	VPOC1, VPOC0 = 0, 1, 1, fall	ling reset voltage	2.68	2.75	2.88	V
	VLVDD3		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	3.13	3.22	3.39	V
				Falling interrupt voltage	3.07	3.15	3.31	V
	VLVDD0		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	4.62	4.74	4.94	V
				Falling interrupt voltage	4.52	4.64	4.84	V

3.6.9 Power supply voltage rising slope characteristics

$(TA = -40 \text{ to } +125^{\circ}C, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				50	V/ms

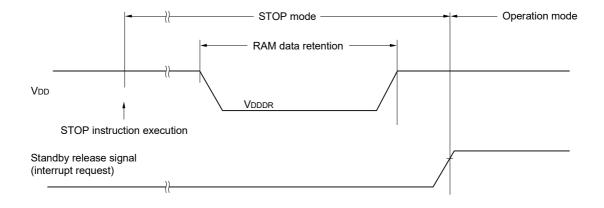
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

$(TA = -40 \text{ to } +125^{\circ}C, Vss = 0 \text{ V}))$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.47 Notes 1, 2		5.5	V

- **Note 1.** The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.
- Note 2. Enter STOP mode before the supply voltage falls below the recommended operating voltage.



3.8 Flash Memory Programming Characteristics

(Ta = -40 to +125°CNote 4, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	2.4 V ≤ VDD ≤ 5.5 V	1		24	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°CNote 5	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°CNote 5		1,000,000		
		Retained for 5 years TA = 85°CNote 5	100,000			
		Retained for 20 years T _A = 85°CNote 5	10,000			

- Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
- Note 2. When using flash memory programmer and Renesas Electronics self-programming library
- **Note 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
- **Note 4.** The range is from TA = -40 to $+105^{\circ}C$ when if the flash memory programmer is in use.
- Note 5. This temperature is the average value at which data are retained.



3.9 Dedicated Flash Memory Programmer Communication (UART)

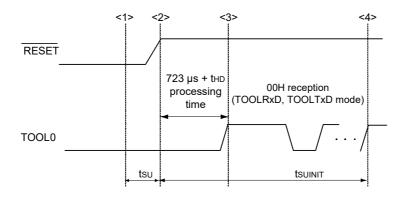
(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.10 Timing for Switching Flash Memory Programming Modes

(TA = -40 to +105°C, 2.4 V \leq AVDD = VDD \leq 5.5 V, AVss = Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	thD	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

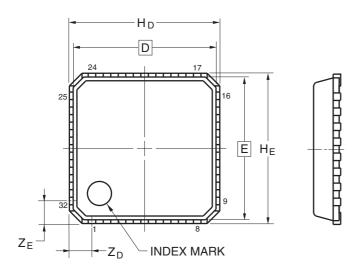
tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
thd: How long to keep the TOOL0 pin at the low level from when the external resets end
(excluding the processing time of the firmware to control the flash memory)

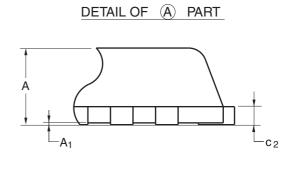
4. PACKAGE DRAWINGS

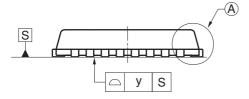
32-pin products 4.1

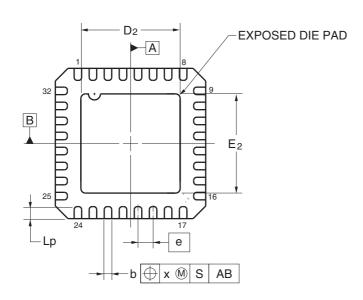
R5F11CBCGNA, R5F11CBCMNA

JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]	
P-HVQFN32-5x5-0.50	PVQN0032KE-A	P32K9-50B-BAH	0.058	







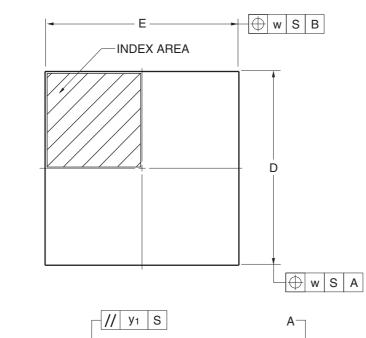


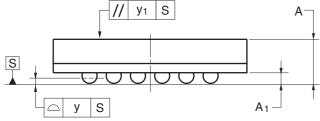
Referance	Dimens	Dimension in Millimeters			
Symbol	Min	Nom	Max		
D		4.75			
E		4.75			
Α			0.90		
A ₁	0.00				
b	0.20	0.25	0.30		
е		0.50			
Lp	0.30	0.40	0.50		
х			0.10		
у			0.05		
H _D	4.95	5.00	5.05		
HE	4.95	5.00	5.05		
Z _D		0.75			
Z _E		0.75			
C ₂	0.19	0.20	0.21		
D ₂		3.30			
E ₂		3.30			

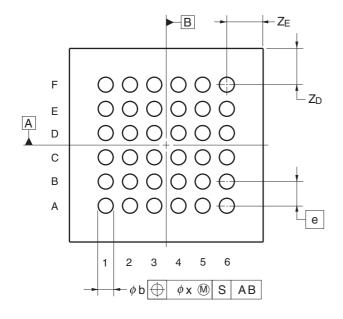
4.2 36-pin products

R5F11CCCGBG, R5F11CCCMBG

JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-TFBGA36-4x4-0.50	PTBG0036KA-A	P36F1-50-AA6	0.027







Referance	Dimens	sion in Mil	Dimension in Millimeters			
Symbol	Min	Nom	Max			
D	3.90	4.00	4.10			
E	3.90	4.00	4.10			
А			1.10			
A ₁	0.17	0.22	0.27			
е		0.50				
b	0.26	0.31	0.36			
х			0.05			
у			0.08			
У1			0.20			
Z _D		0.75				
Z _E		0.75				
w			0.20			

REVISION HISTORY	RL78/I1E Datasheet
------------------	--------------------

Rev.	Date	Description	
		Page	Summary
1.30	Mar 29, 2024	p.3	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/I1E
			Modification of Ordering Part Number in 1.2 Ordering Information
1.20	May 31, 2023	All	The module name for CSI was changed to simplified SPI.
		p.2	Addition of Note in 1.1 Features
		p.3	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/I1E
			Addition of R5F11CBCGNA#00 in Fields of Application Notes G
1.10	Jun 30, 2016	4	Addition of products name in 1.3.1 32-pin products
		5	Addition of products name in 1.3.2 36-pin products
		10	Change of DTC in 1.6 Outline of Functions
		10	Addition of Note1 in 1.6 Outline of Functions
		43	Change of 2.5.1 (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp external clock in input)
		57	Change of 2.7 RAM Data Retention Characteristics
		57	Change of 2.8 Flash Memory Programming Characteristics
		62	Change of 3.2.2 On-chip oscillator characteristics
		91	Change of 3.5.1 (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp external clock in input)
		105	Change of 3.7 RAM Data Retention Characteristics
		105	Change of 3.8 Flash Memory Programming Characteristics
1.00	Jul 31, 2015	_	First Edition issued

All trademarks and registered trademarks are the property of their respective owners.

General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).

7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

Notice

- 1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation or any other use of the circuits, software, and information in the design of your product or system. Renesas Electronics disclaims any and all liability for any losses and damages incurred by you or third parties arising from the use of these circuits, software, or information.
- Renesas Electronics hereby expressly disclaims any warranties against and liability for infringement or any other claims involving patents, copyrights, or other intellectual property rights of third parties, by or arising from the use of Renesas Electronics products or technical information described in this document, including but not limited to, the product data, drawings, charts, programs, algorithms, and application examples.
- No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
- 4. You shall be responsible for determining what licenses are required from any third parties, and obtaining such licenses for the lawful import, export, manufacture, sales, utilization, distribution or other disposal of any products incorporating Renesas Electronics products, if required.
- 5. You shall not alter, modify, copy, or reverse engineer any Renesas Electronics product, whether in whole or in part. Renesas Electronics disclaims any and all liability for any losses or damages incurred by you or third parties arising from such alteration, modification, copying or reverse engineering.
- 6. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The intended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.
 - "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; industrial robots; etc.
 - "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control (traffic lights); large-scale communication equipment; key financial terminal systems; safety control equipment; etc.

Unless expressly designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not intended or authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems; surgical implantations; etc.), or may cause serious property damage (space system; undersea repeaters; nuclear power control systems; aircraft control systems; key plant systems; military equipment; etc.). Renesas Electronics disclaims any and all liability for any damages or losses incurred by you or any third parties arising from the use of any Renesas Electronics product that is inconsistent with any Renesas Electronics data sheet, user's manual or other Renesas Electronics document.

- 7. No semiconductor product is absolutely secure. Notwithstanding any security measures or features that may be implemented in Renesas Electronics hardware or software products, Renesas Electronics shall have absolutely no liability arising out of any vulnerability or security breach, including but not limited to any unauthorized access to or use of a Renesas Electronics product or a system that uses a Renesas Electronics product. RENESAS ELECTRONICS DOES NOT WARRANT OR GUARANTEE THAT RENESAS ELECTRONICS PRODUCTS, OR ANY SYSTEMS CREATED USING RENESAS ELECTRONICS PRODUCTS WILL BE INVULNERABLE OR FREE FROM CORRUPTION, ATTACK, VIRUSES, INTERFERENCE, HACKING, DATA LOSS OR THEFT, OR OTHER SECURITY INTRUSION ("Vulnerability Issues"). RENESAS ELECTRONICS DISCLAIMS ANY AND ALL RESPONSIBILITY OR LIABILITY ARISING FROM OR RELATED TO ANY VULNERABILITY ISSUES. FURTHERMORE, TO THE EXTENT PERMITTED BY APPLICABLE LAW, RENESAS ELECTRONICS DISCLAIMS ANY AND ALL WARRANTIES, EXPRESS OR IMPLIED, WITH RESPECT TO THIS DOCUMENT AND ANY RELATED OR ACCOMPANYING SOFTWARE OR HARDWARE, INCLUDING BUT NOT LIMITED TO THE IMPLIED WARRANTIES OF MERCHANTABILITY, OR FITNESS FOR A PARTICULAR PURPOSE.
- 8. When using Renesas Electronics products, refer to the latest product information (data sheets, user's manuals, application notes, "General Notes for Handling and Using Semiconductor Devices" in the reliability handbook, etc.), and ensure that usage conditions are within the ranges specified by Renesas Electronics with respect to maximum ratings, operating power supply voltage range, heat dissipation characteristics, installation, etc. Renesas Electronics disclaims any and all liability for any malfunctions, failure or accident arising out of the use of Renesas Electronics products outside of such specified ranges.
- 9. Although Renesas Electronics endeavors to improve the quality and reliability of Renesas Electronics products, semiconductor products have specific characteristics, such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Unless designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not subject to radiation resistance design. You are responsible for implementing safety measures to guard against the possibility of bodily injury, injury or damage caused by fire, and/or danger to the public in the event of a failure or malfunction of Renesas Electronics products, such as safety design for hardware and software, including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult and impractical, you are responsible for evaluating the safety of the final products or systems manufactured by you.
- 10. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. You are responsible for carefully and sufficiently investigating applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive, and using Renesas Electronics products in compliance with all these applicable laws and regulations. Renesas Electronics disclaims any and all liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
- 11. Renesas Electronics products and technologies shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You shall comply with any applicable export control laws and regulations promulgated and administered by the governments of any countries asserting jurisdiction over the parties or transactions.
- 12. It is the responsibility of the buyer or distributor of Renesas Electronics products, or any other party who distributes, disposes of, or otherwise sells or transfers the product to a third party, to notify such third party in advance of the contents and conditions set forth in this document.
- 13. This document shall not be reprinted, reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
- 14. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products.
- (Note1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its directly or indirectly controlled subsidiaries.
- (Note2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

(Rev.5.0-1 October 2020)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.

Contact Information

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit: www.renesas.com/contact/